DIGMAPS: a standalone tool to study digitization

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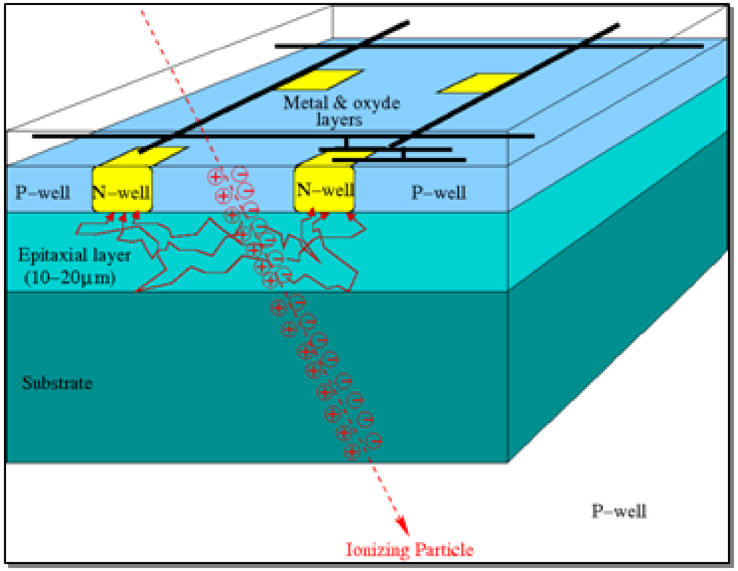
thanks to A.Geromitsos and J.Baudot for fruitful discussions

Why a digitizer tool for MAPS ?

- 2 mains motivations
  - Help to optimize design for a given application, e.g.
    - N bits of ADCs, Discriminator thresholds,
    - occupancy, hit separation,
    - Pitch, number of layers, etc.
    - Etc.
  - Test model for simulation
    - Fast or full simulation for many applications
- 1 long term goal
  - Get a full simulation chain
    - Geant 4 + digitizer + tracking/reco
    - Alignment studies (e.g. AIDA)
- 1 road map
  - Build a data driven model
    - to take advantage of our knowledge coming from ~30 beam test campaigns
    - Because a pure realistic analytical model is difficult to build

What do we want to simulate ?

- Step 1: incident particle generation
  - Nature, energy spectrum, incident angle spectrum
    - Beam test, beamstrahlung spectrum for ILC, etc.
- Step 2: energy deposition ⇨ charge generation
  - Landau law (MPV = 80 e- / um)
- Step 3: charge transport up to the N-well diodes
  - Charge sharing between pixels
  - Recombination, charge collection efficiency
  - Reflexion at the epi/substrate interface
  - Noise, fake pixels
- Step 4: digital part
  - Discriminator / ADC dynamic range
  - Zero suppression stage
- Step 5: clustering algorithms
  - Resolution, hit separation
- Step 6: (not included) tracking, vertexing etc.



- Test Criteria:
  - Realistic performances
    - Efficiency,
    - resolution,
    - fake rate
  - Charge sharing
    - occupancy (multiplicity)
    - Hit separation

DIGMAPS: a standalone digitizer tool

- MAPS Digitizer (DIGMAPS)
  - From particle generation
  - To the digitizer
- Library running in root
  - Easy to load
  - Easy to run

```
{
  gROOT->ProcessLine(".L digaction.cxx+");
  gROOT->ProcessLine(".L digadc.cxx+");
  gROOT->ProcessLine(".L digbeam.cxx+");
  gROOT->ProcessLine(".L digplane.cxx+");
  gROOT->ProcessLine(".L digparticle.cxx+");
  gROOT->ProcessLine(".L digreadoutmap.cxx+");
  gROOT->ProcessLine(".L digcluster.cxx+");
  gROOT->ProcessLine(".L digevent.cxx+");
  gROOT->ProcessLine(".L diginitialize.cxx+");
  gROOT->ProcessLine(".L  dighistograms.cxx+");
  gROOT->ProcessLine(".L digmaps.cxx+");
  //   gROOT->ProcessLine(".L digproto.cxx+");

}
```

```
DIGMAPS  myDIGMAPS("name","title", "~/mydircode/","input.txt","~/myoutputdir","output.txt","foresee")
```

  - All output stored in Root format
    - .x Read.C ; .x Plot.C

```
Int_t myconfig = 1;
myDIGMAPS2.PrintConfigurations() ;
myDIGMAPS2.PlotAConfiguration(myconfig,1);
```

- Input data cards to compare any configurations

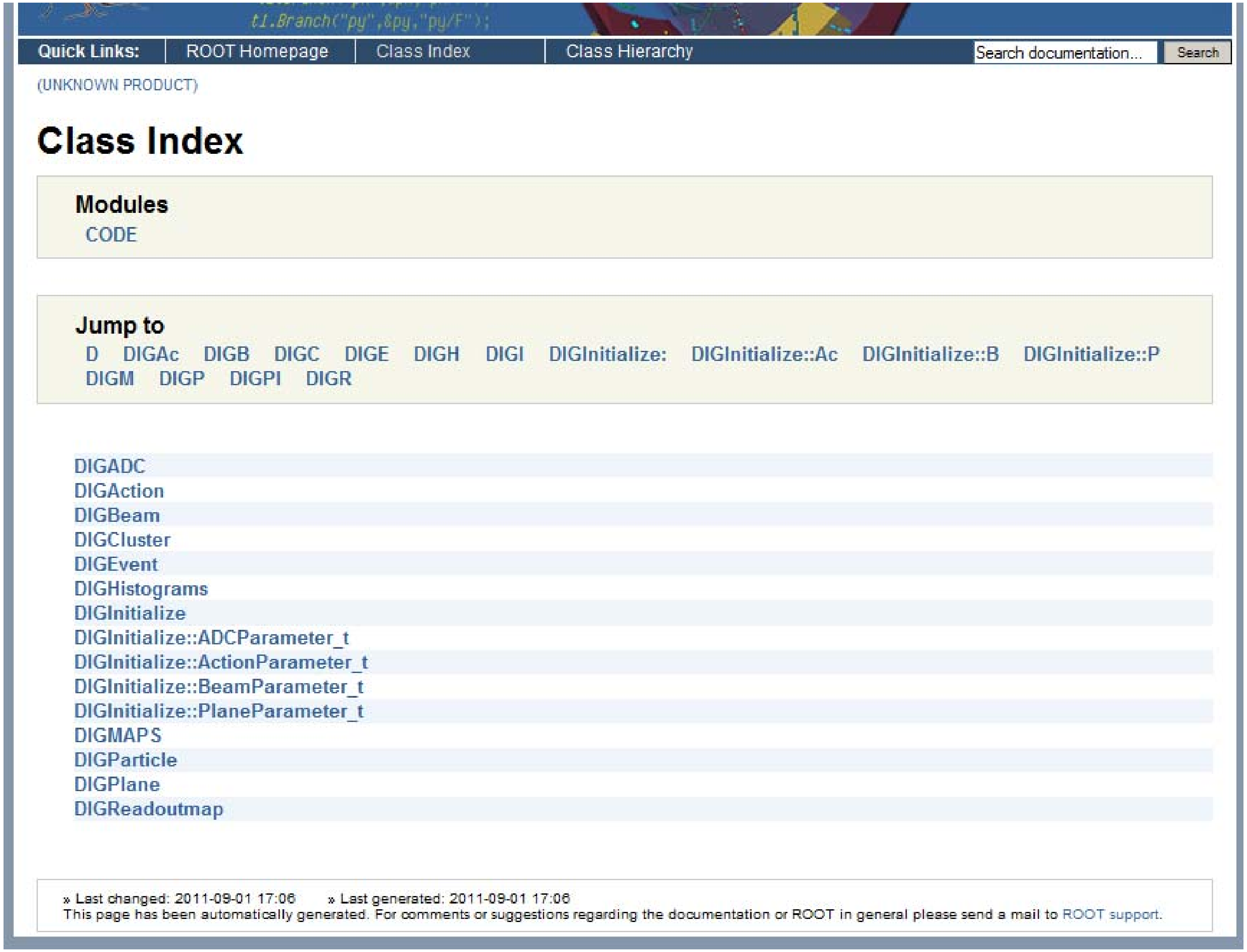
```
// -+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-
//
// This is a Configuration File for Silicon Tracking Analysis DIGMAPS Package
//
// created    -> 18/03/2011
// Author = Auguste Besson abesson@in2p3.fr
// -+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-
// ------------------- !!!! DO NOT USE Colons in Comments !!! ---
//
// -+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-
// Action Parameter
// -+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-
// chose the action -> foresee = model result ; train = adjust/fit
//  plot = fill histograms from the tree.
//Doit "foresee"
Model: "basic"

// -+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-
// BEAM Parameter
// -+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-
RunNumber: 1000
NumberOfEvents: 10000
// Beam generation option.
//1=realistic beam with random number of particle per event
//2=1 particle per event with a hit in a central pixel
BeamOption: 2
//number of particles per mm^2 on the Plane per event (Lambda fact
ParticleDensity: 5.0
//ParticleDensityWidth 0.5
// incident angle in degrees in cylindrical coordinates (theta and
NAngles: 3
ThetaIncidentDeg 0.0 10.0 20.0
PhiIncidentDeg   0.0  0.0 45.0
// -+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-
// PLANE Parameters
// -+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-
//-----------GENERAL GEOMETRY
//---pixel pitch in X and Y in microns
NGeom: 4
PitchX:             10.00 20.00 30.00 40.00
PitchY:             10.00 20.00 30.00 40.00
//---Noise in electrons
NoiseElectrons:     10.85  9.20  9.40  9.80
//---epitaxial thickness in microns
EpitaxialThickness: 12.65 10.80  8.69  7.78
//-----------OTHER PARAMETERS
//---number of pixels
NpixelsX: 21
NpixelsY: 21
//---Chip temperature
NTemperature: 1
Temperature: 10
//-----------CHARGE TRANSPORT
//---ionization energy (eV)
IonizationEnergy: 3.6
//---Starting Segment size (in microns)
SegmentSize: 0.1
//---Maximum Segment size (in microns)
MaximumSegmentSize: 1.0
//---Maximum Charge Per Segment (in electrons)
MaximumChargePerSegment: 1.0
//---Diffusion Maximum Range in X and Y (in pitch units)
DiffusionMaximumRangeInX: 2.5
DiffusionMaximumRangeInY: 2.5
//---Reflexion Coefficient on the subtrat-epi border (1.0 means 100%) NOT USED
ReflexionCoefficient: 1.0
```

```
//------------CHARGE TRANSPORT MODEL
//---basic model
//---sigma of the gaussian width dispersion of charge at 10 microns depth
BasicModel_SigmaTenMicrons: 10.0
//---Chose Model (1=Lorentz2D , 2=Gauss2D)
ChargeModel: 2
//---Lorentz2D model
//---C term of the Lorentz width dispersion
Lorentz2DModel_Cp0: 0.6607
Lorentz2DModel_Cp1: 0.40  //0.400664
Lorentz2DModel_RangeLimit_InPitchUnit: 2.5
//---Gauss2D Model
//sum of 2d gaussian The sigma are lineary dependant to the pitch
Gauss2DModel_sigma1_Cp0: 1.12
Gauss2DModel_sigma1_Cp1: 0.35
Gauss2DModel_sigma2_Cp0: 1.16
Gauss2DModel_sigma2_Cp1: 0.83
Gauss2DModel_weight: 0.34
// -+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-
// ADC Parameters
// -+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-+-
// number of different ADC to test
NADC: 3
// ADC parameters
// Nbits = number of bits of the ADC. There will be (2^Nbits - 1) thresholds.
// LSB, Electron_Conversion and ADC_thresholds are in Noise multiple units (e.g. 2.0 = 2.0 t
// There are 2 different ways to set the ADC
// ----------- EITHER --------------
// 1/ ADC_linear = 1 (the response is linear, so setting the LSB and
// the Electron Conversion factor allow to compute all thresholds.
// = thresholds will be = LSB, LSB+1xElectron_conversion, LSB+2xElectron_conversion etc.
// LSB= 1.5 = threshold of the first significant bit
// Electron_Conversion= 1.5
// ADC_thresholds= -
// ----------- OR --------------
// 2/ ADC_linear = 0 (the response is not linear, so enter all the different threshold values
// LSB= -
// Electron_Conversion= -
// ADC_thresholds= 2.0 4.0 5.0 etc.
// ---ADC 1
Nbits: 1
ADC_linear: 0
LSB: -
Electron_Conversion: -
ADC_thresholds: 5.0
// ---ADC 2
Nbits: 12
ADC_linear: 1
LSB: 0.64
Electron_Conversion: 0.64
ADC_thresholds: -
// ---ADC 3
Nbits: 12
ADC_linear: 1
LSB: 0.60
Electron_Conversion:  0.60
ADC_thresholds: -
```

- Many input parameters:
  - ➢Beam (flux, angle)
  - ➢MAPS (pitch, noise, epi. Layer)
  - ➢Charge transport Model
  - ➢ADC/discri threshold
  - ➢Etc.

(under developpment)

DIGMAPS: Root-Html doc



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(UNKNOWN PRODUCT)

Class Index

Modules

CODE

Jump to

D DIGAc DIGB DIGC DIGE DIGH DIGI DIGInitialize: DIGInitialize::Ac DIGInitialize::B DIGInitialize::P DIGM DIGP DIGPI DIGR

DIGADC
DIGAction
DIGBeam
DIGCluster
DIGEvent
DIGHistograms
DIGInitialize
DIGInitialize::ADCParameter_t
DIGInitialize::ActionParameter_t
DIGInitialize::BeamParameter_t
DIGInitialize::PlaneParameter_t
DIGMAPS
DIGParticle
DIGPlane
DIGReadoutmap

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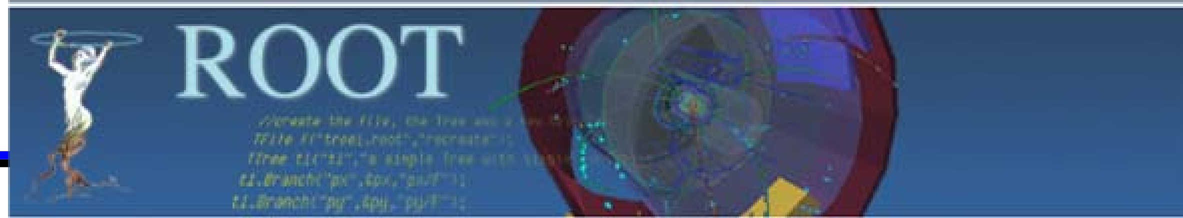


Quick Links: ROOT Homepage | Class Index | Class Hierarchy | Search documentation... Search
Source: header file | source file | inheritance tree (.pdf) | viewVC header | viewVC source
Sections: class description | function members | data members | class charts

(UNKNOWN PRODUCT) » CODE » DIGParticle

class DIGParticle: public TObject

```
Double_t DIGParticle::Lorentz2D(Double_t *x, Double_t *par){
```

Function Members (Methods)

public:

```
                  DIGParticle ()
                  DIGParticle (DIGParticle& adigparticle)
                  DIGParticle (Float_t EntryX, Float_t EntryY, Float_t EntryZ, Float_t ExitX, Float_t ExitY, Float_t ExitZ, Float_t
                      Energy_deposited)
          virtual ~DIGParticle ()
             void AddPixel (Float_t AnalogCharge, Int_t PixelNumber)
             void AddRandomNoise (DIGPlane* myDIGPlane)
             void AnalogToDigitalconversion (DIGADC* myDIGADC, DIGPlane* myDIGPlane)
   static TClass* Class ()
     virtual void Clear (Option_t* = "")
             void ComputeChargeDeposition (Float_t StartingSegmentSize, Float_t MaximumSegmentSize, Float_t
                      MaximumChargePerSegment)
             void ComputeChargeTransport (DIGPlane* aDIGPlane)
         Double_t GaussianLaw (Double_t mean, Double_t sigma)
 vector<Float_t> GetAnalogCharge ()
   vector<Int_t> GetDigitalCharge ()
          Float_t GetEnergy_deposited ()
          Float_t GetEntryX ()
          Float_t GetEntryY ()
          Float_t GetEntryZ ()
          Float_t GetExitX ()
          Float_t GetExitY ()
          Float_t GetExitZ ()
            Int_t GetNpixels ()
            Int_t GetNSegment ()
   vector<Int_t> GetPixelMap ()
            Int_t GetPixelNumber (DIGPlane* myDIGPlane, Float_t Xpos, Float_t Ypos)
 vector<Float_t> GetSegmentCharge ()
 vector<Float_t> GetSegmentX ()
 vector<Float_t> GetSegmentY ()
```

DIGMAPS: Root-Html doc

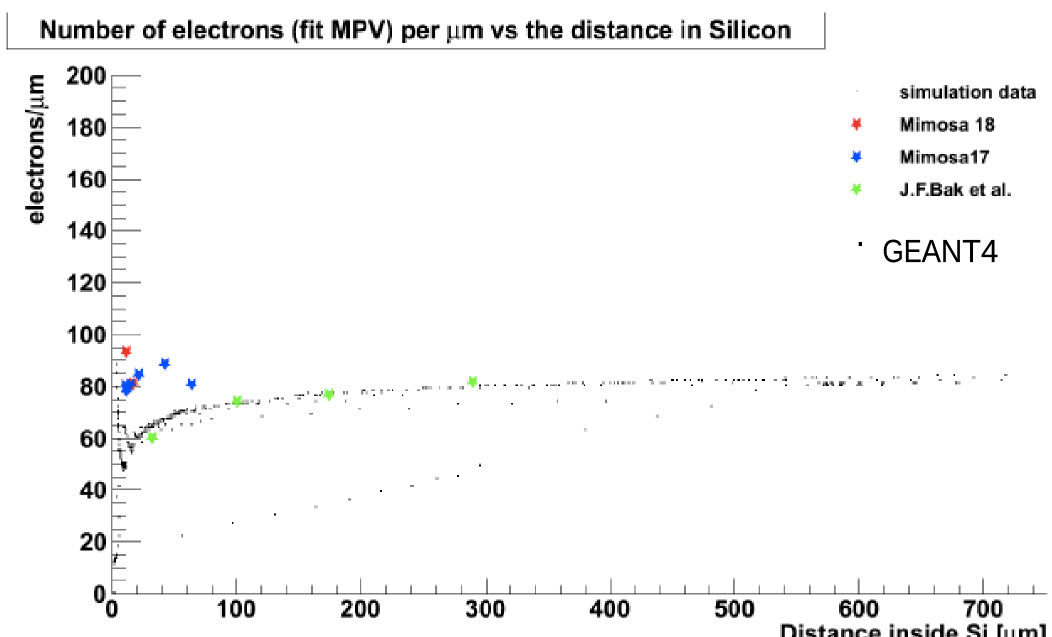
```
}
//______________________________________________________________________________
//
void DIGParticle::ComputeChargeDeposition(Float_t StartingSegmentSize, Float_t MaximumSegmentSize,
                                          Float_t MaximumChargePerSegment)
{
  Float_t SegmentSize = StartingSegmentSize;
  Float_t TotalLength = TMath::Sqrt((fExitX-fEntryX)*(fExitX-fEntryX)
                                    +(fExitY-fEntryY)*(fExitY-fEntryY)
                                    +(fExitZ-fEntryZ)*(fExitZ-fEntryZ));

  Float_t ChargePerSegment = 0.0;
  if(SegmentSize<0.0){
    SegmentSize=0.001;
  }
  fNSegment = int(TotalLength*1.000001/SegmentSize) ;
  if(fNSegment<1){
    fNSegment=1;
  }
  SegmentSize = TotalLength/float(fNSegment);
  ChargePerSegment = fEnergy_deposited / float(fNSegment);

  while((SegmentSize>MaximumSegmentSize)&&(ChargePerSegment > MaximumChargePerSegment)){
    Int_t newNSegment = int(fNSegment *1.1);
    if(newNSegment==fNSegment){fNSegment++;}
    SegmentSize = TotalLength/float(fNSegment);
    ChargePerSegment = fEnergy_deposited / float(fNSegment);
  }
  Float_t xstep = fExitX-fEntryX;
  Float_t ystep = fExitY-fEntryY;
  Float_t zstep = fExitZ-fEntryZ;


  for (Int_t i=0 ; i<fNSegment ; i++){
    fSegmentX.push_back(fEntryX + (float(i+0.5)* xstep/float(fNSegment)) );
    fSegmentY.push_back(fEntryY + (float(i+0.5)* ystep/float(fNSegment)) );
    fSegmentZ.push_back(fEntryZ + (float(i+0.5)* zstep/float(fNSegment)) );
    fSegmentCharge.push_back(ChargePerSegment );
  }


}
//______________________________________________________________________________
//
```

Step 2: Energy deposition

- Potential tricky issues:
  - What about charge created inside the diode ?
  - Is the Epitaxial layer thickness really known ?
  - Is GEANT4 able to compute energy deposition in very thin material (10-20 um) ?

Energy deposition in thin silicon devices (A.Geromitsos)

Number of e^- created per µm (MPV value)

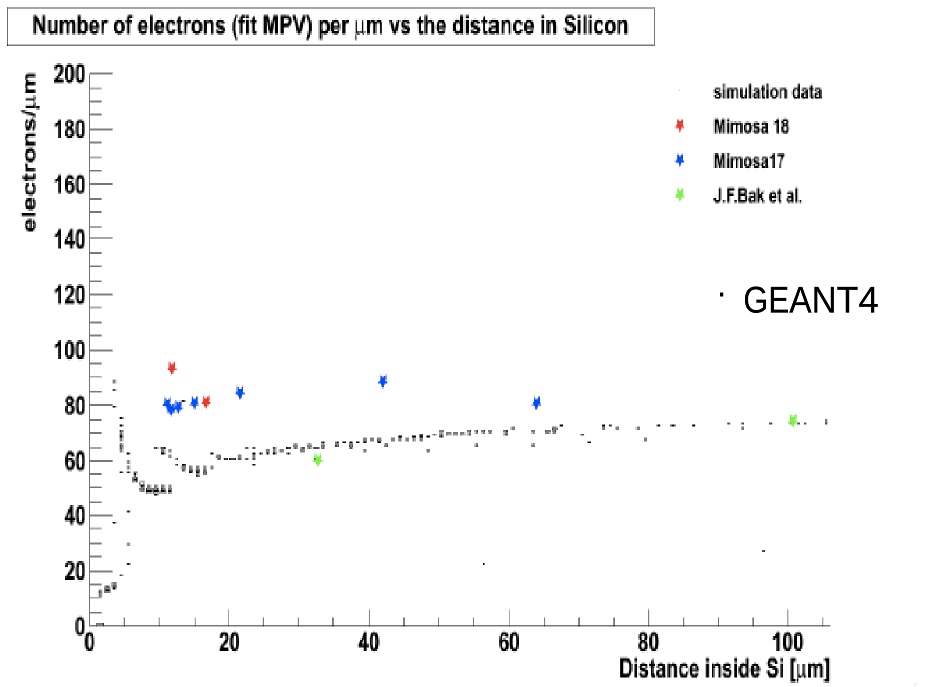


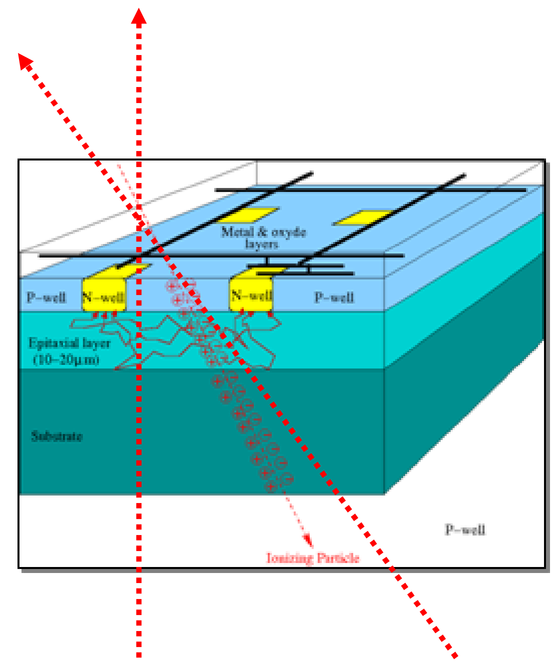
Effective « Thickness » of the epitaxial layer (µm)

Step 2: Energy deposition in thin silicon devices (A.Geromitsos)

- (large values obtained with large incident angle)
  - GEANT4 underestimate charge creation for thin devices
    - ➢ Charge creation taken from test beam data

NOTE: No charge collection efficiency taken into account for M17 and M18

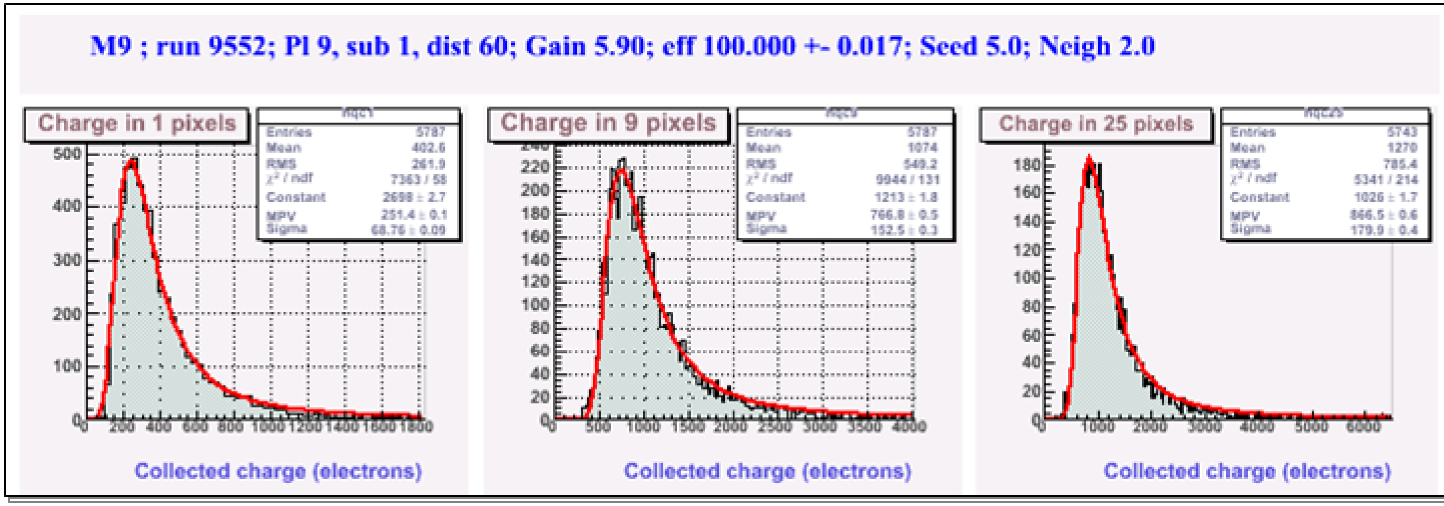


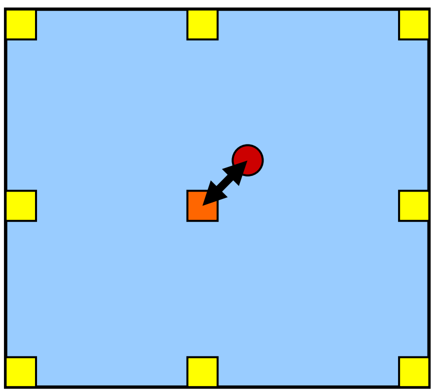


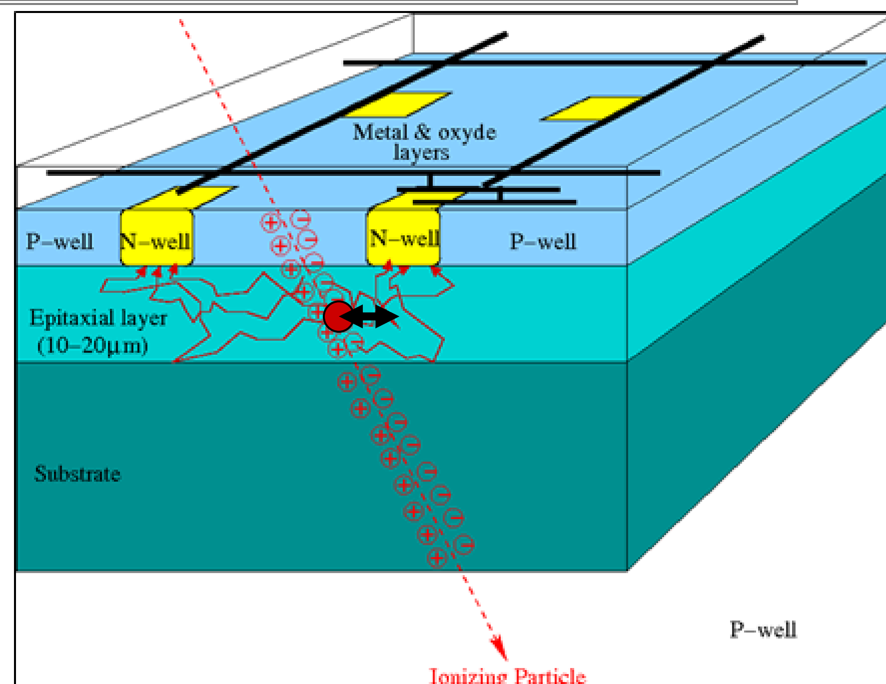
⇨ Chose a Landau with a MPV=80 e-/μm

Large incident angle = increased effective thickness of the epi. layer

Seed impact distance and charge collection





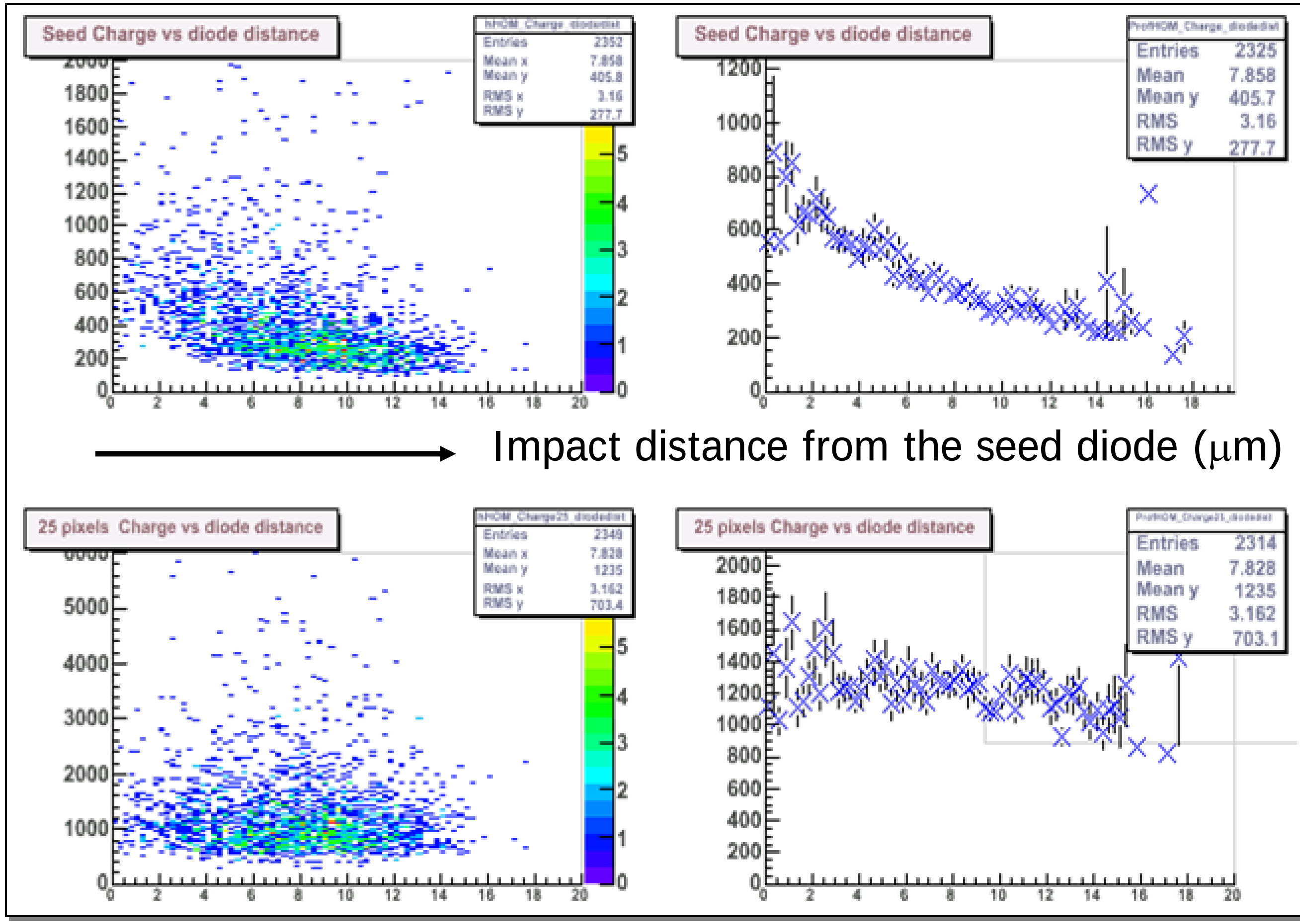


- = Collecting diodes
- = seed diode
- = Impact position
- = seed-impact distance

Charge vs seed-impact distance

Collected charge (e-)
In seed pixel

Collected charge (e-)
in the whole
cluster (5x5)



- Charge in seed depends highly on impact position but total charge is « almost » constant
  - Global Charge collection efficiency is constant as a first good approximation
  - We can separate charge creation and charge collection in 2 independent steps.
  - Charge creation can be parametrized with on only one parameter = Effective epitaxial thickness for a given prototype

Step 3: Charge transport and charge collection

- Goal
  - Build a data driven model with a reasonable number of parameters
- Physical parameters:
  - Collecting charge diode (N-Well)
    - ➢ pitch
    - ➢ Surface
    - ➢ Depleted region
  - Doping profile
    - ➢ Epitaxial layer thickness
    - ➢ Epitaxial layer – Substrate interface
      Perfect reflexion of charge ?
    - ➢ Charge Collection Efficiency
      Is it constant ?

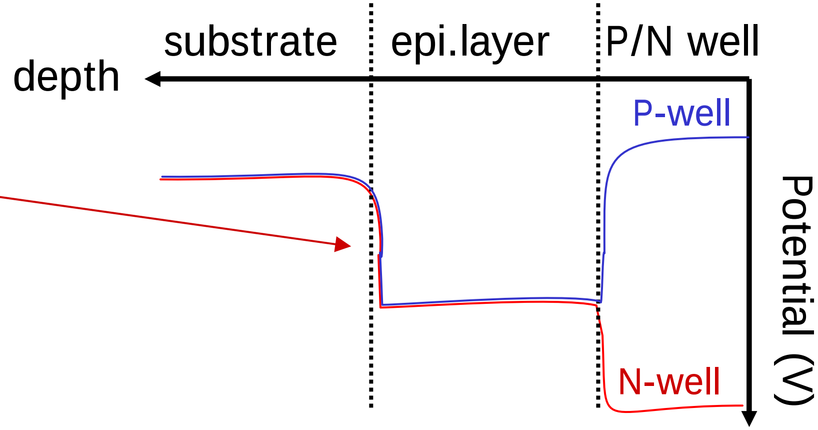
  } Not always known perfectly (e.g. doping profile)

- From our data
  - Total collected charge (e^-)
  - Charge distribution between pixels
  - Noise (e^-)
  - Charge collection efficiency (>~90-95%)
    - ➢ Effective epitaxial thickness
  - ADC gain and dynamic range

  } Measurable from lab and beam test (easier with analog ouput !)

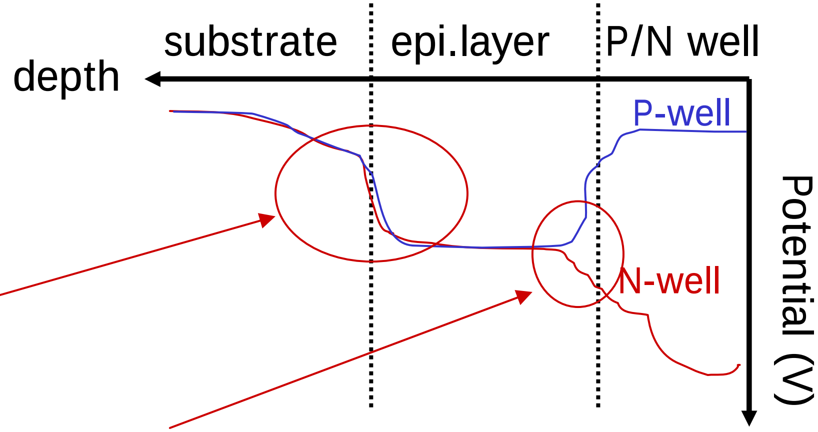
Step 3: Potential profile

- Schematical profile
  - Ideal case



➢ Measure an effective epitaxial layer

For each prototype

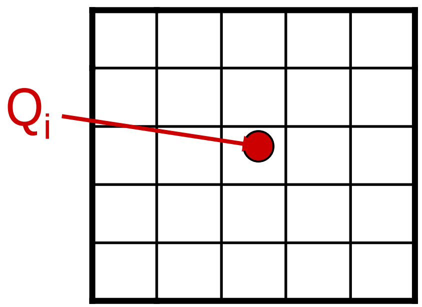


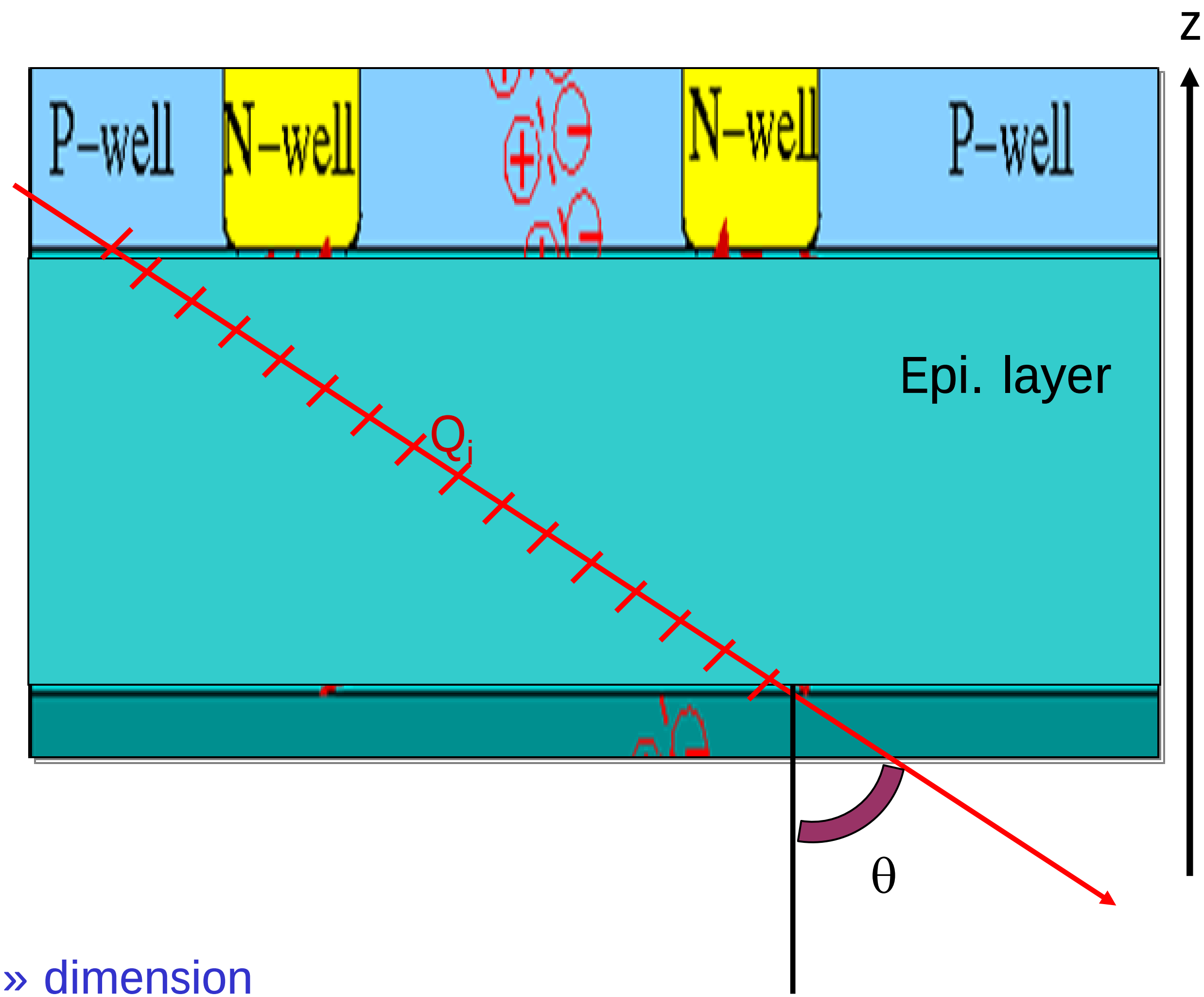
Not so sharped region

depleted region

Step 3: segmentisation

- Divide the track
  - N segments i
  - Q_i = Qtot /N
- Q_i can be as low as 1 e-
  - More CPU
  - More detailed
  - Option assumed in the following slides
- compute 25 probabilities of Charge Qi to reach pixel j(1,25)





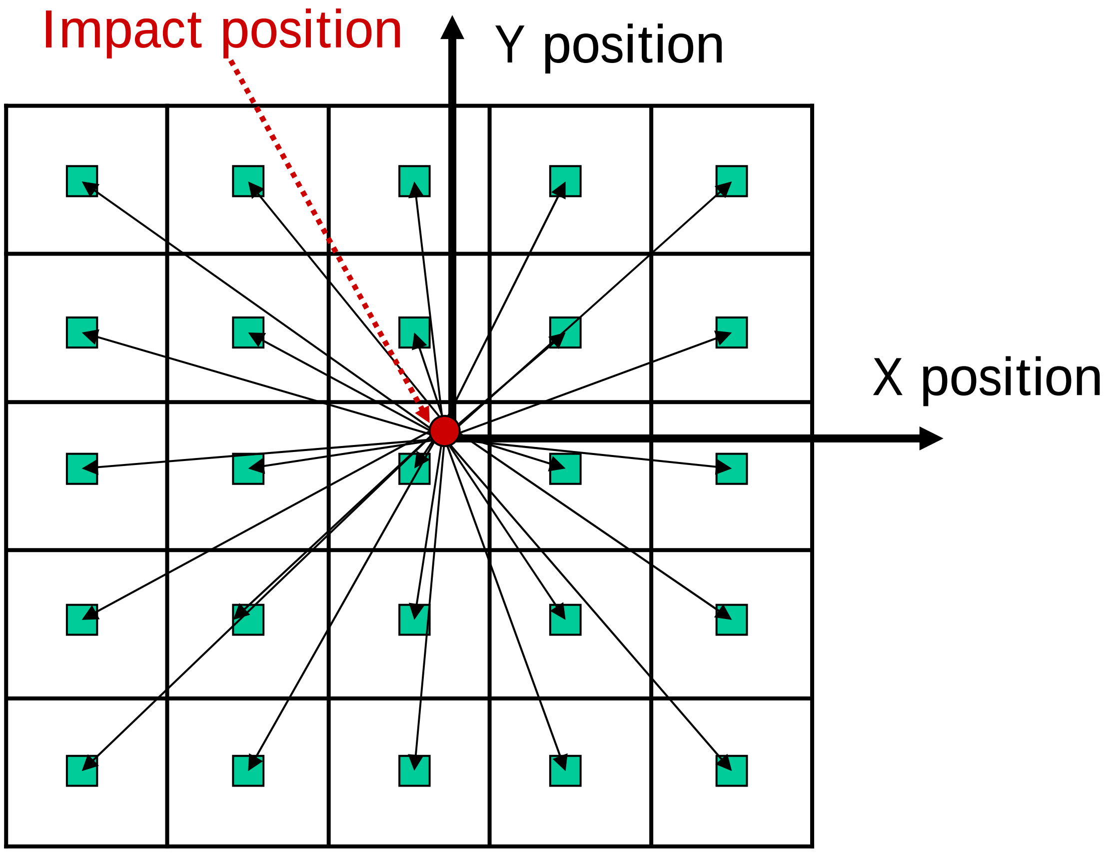
- Model independant of « z » dimension
  - But able to deal with tracks having $\theta \neq 0$

Step 3: What we konw/observe from our data

- Results taken from Mimosa 9/18 chips
  - (AMS-opto 0.35, not HR)
  - Analog output (actually 12bits ADC)
  - 10,20,30,40 um pitch
- Informations provided by beam test/lab test
  - Gain (e-/ADC)
  - Charge collection efficiency
  - Effective epitaxial layer thickness
    - ➢ Obtained from cluster total charge
  - Performances
    - ➢ S/N, efficiency, fake rate, resolution, multiplicity, etc.
- Chips with digital output (STAR, CBM, ILC 1st layer, etc.)
  - No charge recorded
    - ➢ Threshold scans

Collected charge vs impact position

- For each event
  - Impact position from the telescope defines the origin
  - Store 25 x 3D vectors
    - {x(μm), y(μm), Q(e^-)}

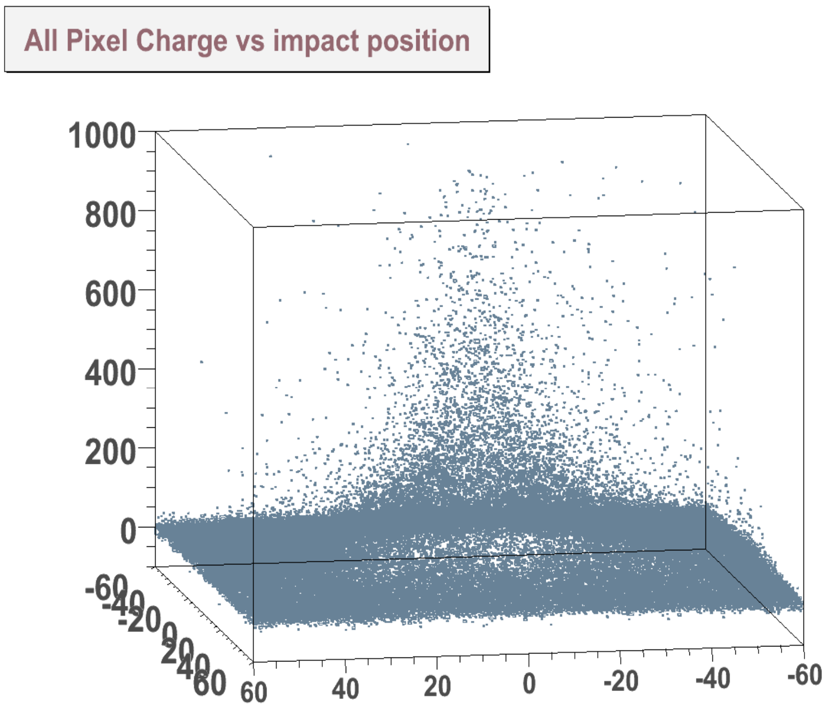


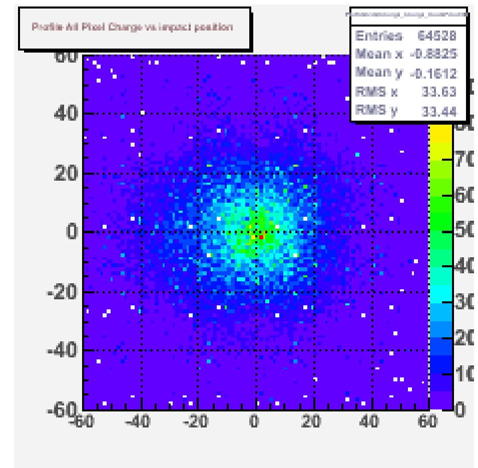
- Plot all this vectors in a Single 3D plot

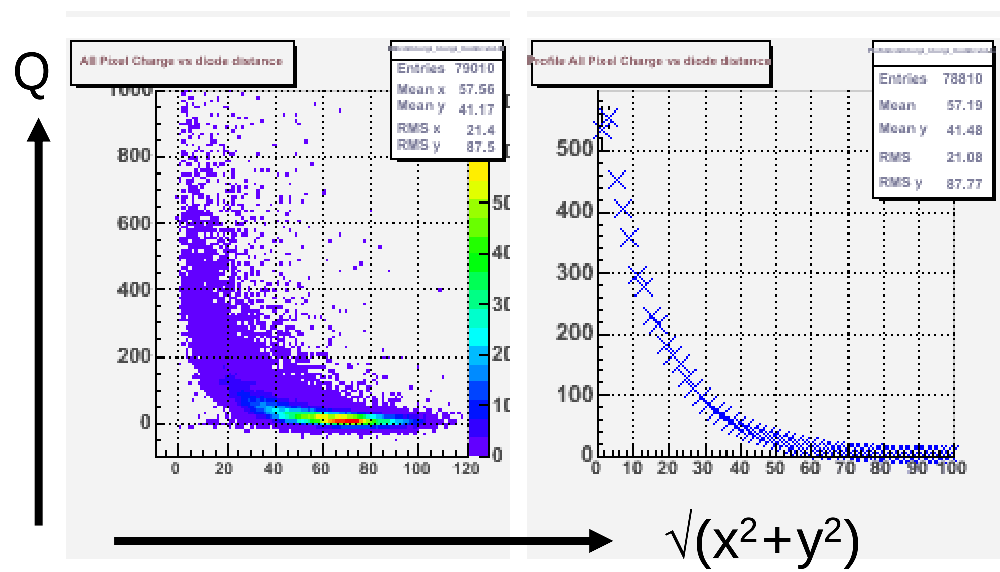
- All the useful information should be contained in this plot
  - Use it as a probability density function

Collected charge vs impact position (2)

- Example (30 um pitch)



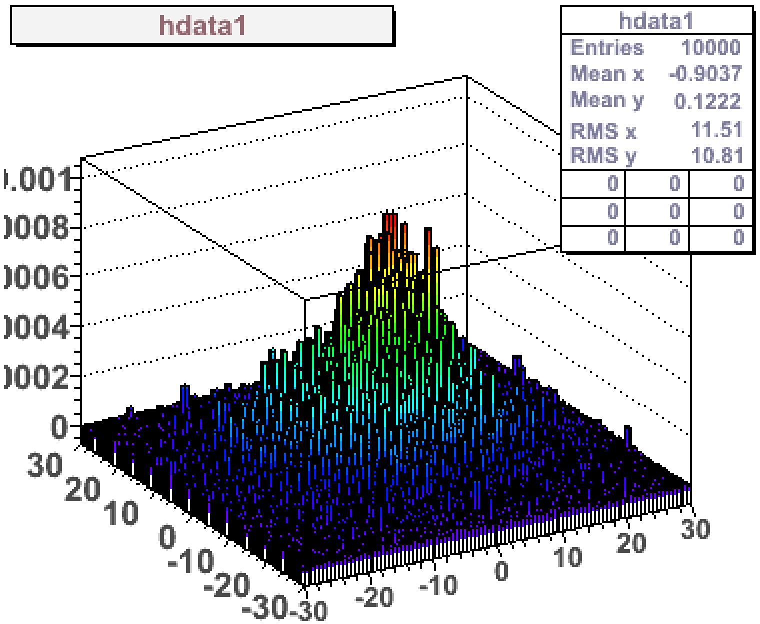


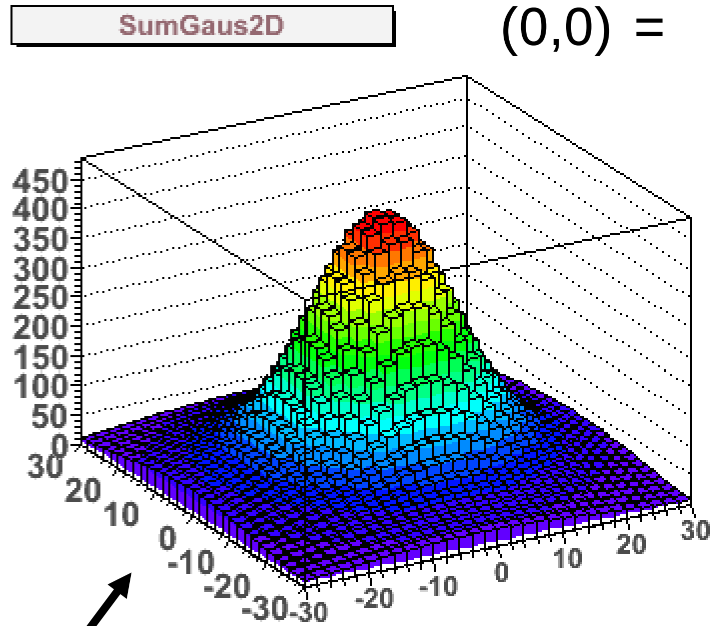


Collected charge vs impact position (4)

- Take the profile of the previous plots and fit it with
  - F(x,y) = sum of 2 x 2Dgaussian

$$e^{-\frac{x^2+y^2}{2\sigma_1^2}} + w \times e^{-\frac{x^2+y^2}{2\sigma_2^2}}$$



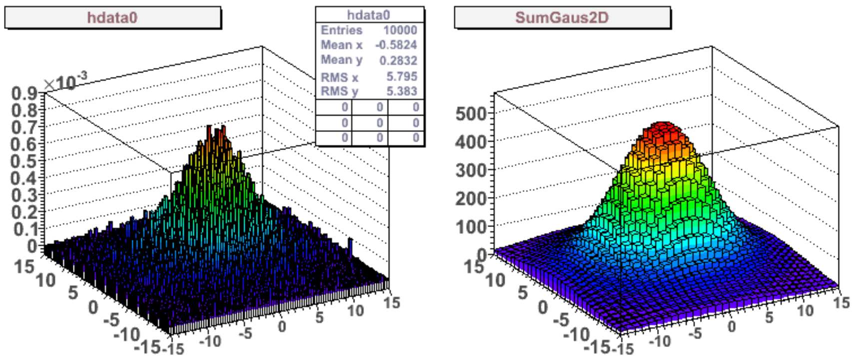


(0,0) =

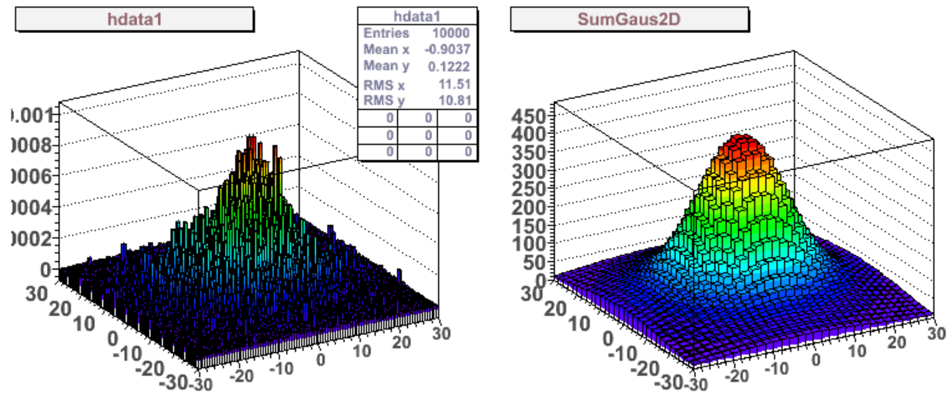
Defines a probabilty density function for charge Q_i to reach pixel j which is at (x,y) w.r.t. the impact

⇨ 25 probabilities

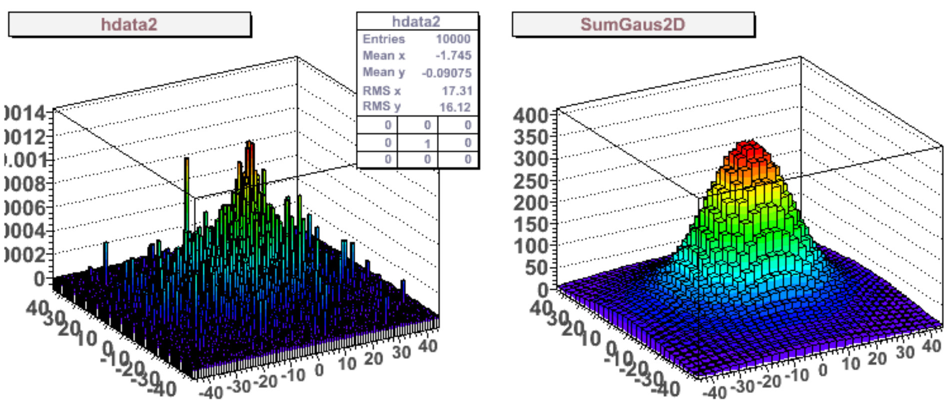
Collected charge vs impact position (3)



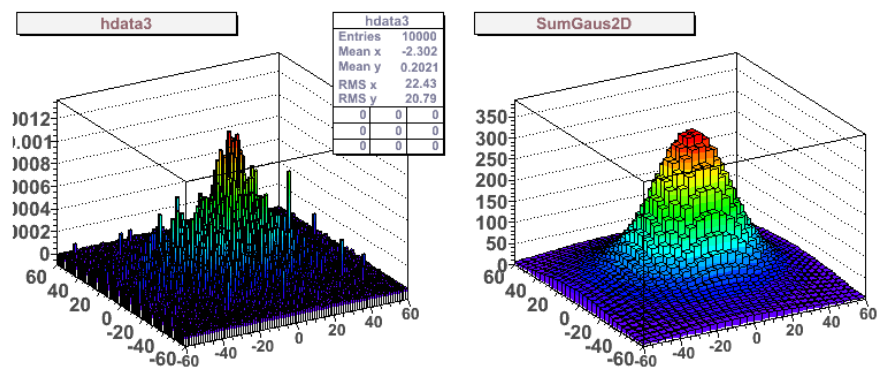
10 μm pitch



20 μm pitch



30 μm pitch

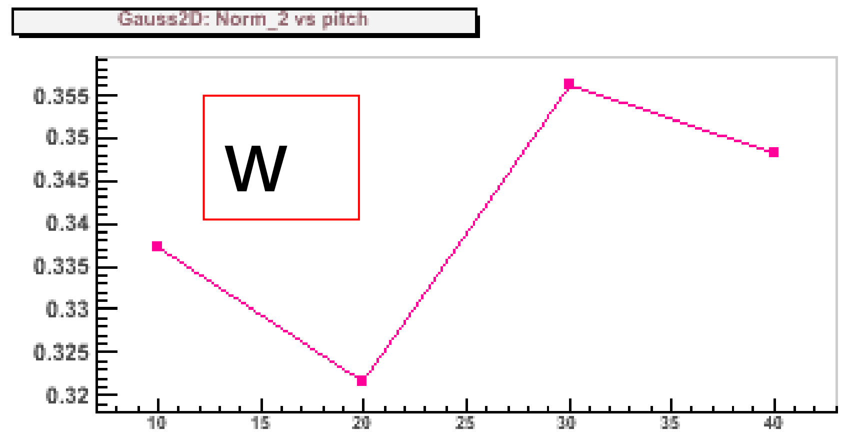


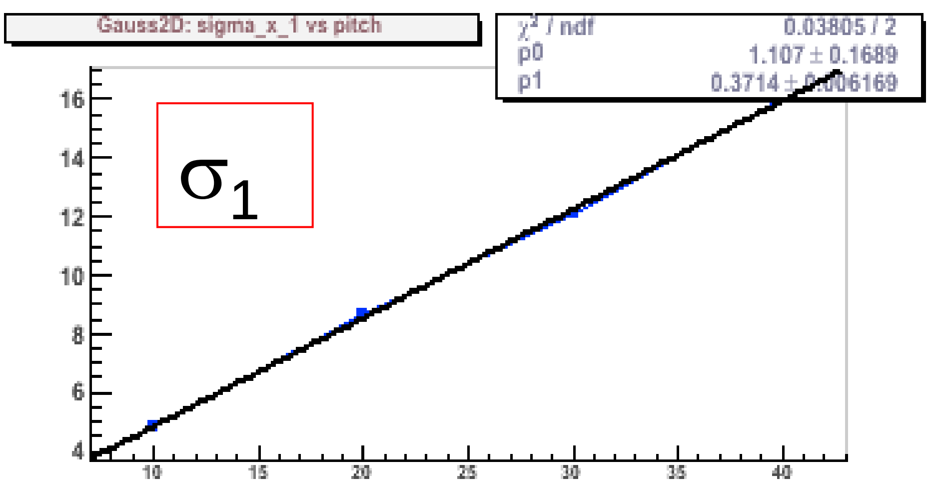
40 μm pitch

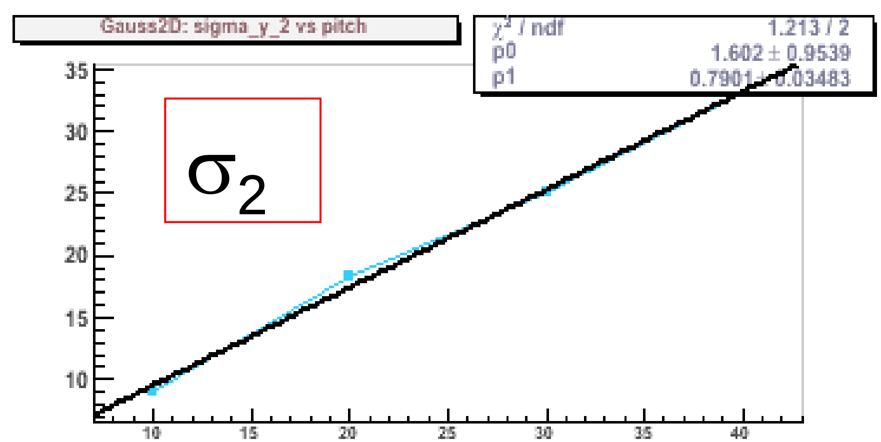
Collected charge vs impact position (5)

- Linearity vs pitch ⇨ 5 parameters for all pitches

$$e^{-\frac{x^2+y^2}{2\sigma_1{}^2}} + w \times e^{-\frac{x^2+y^2}{2\sigma_2{}^2}}$$







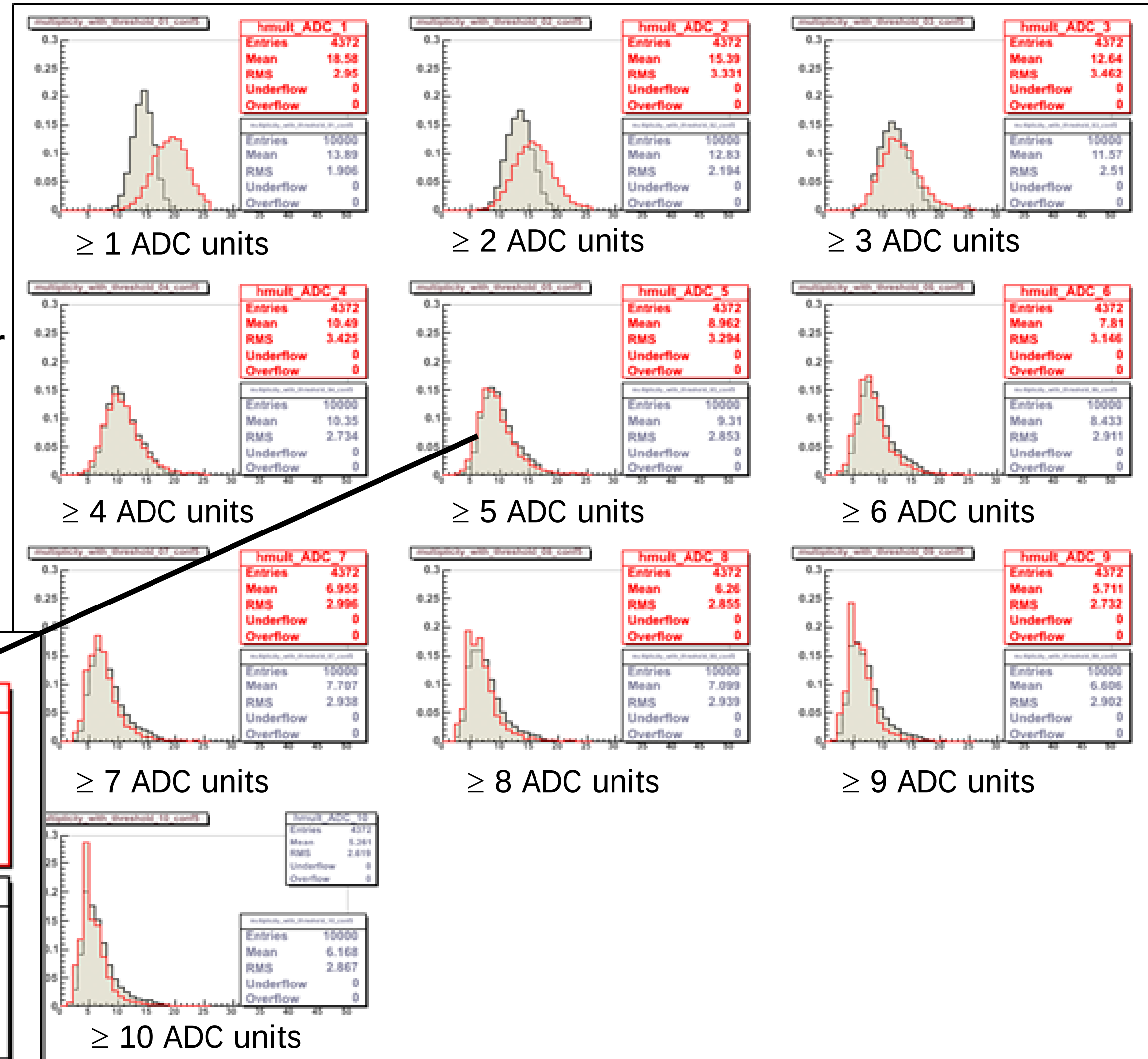
Pitch (μm)

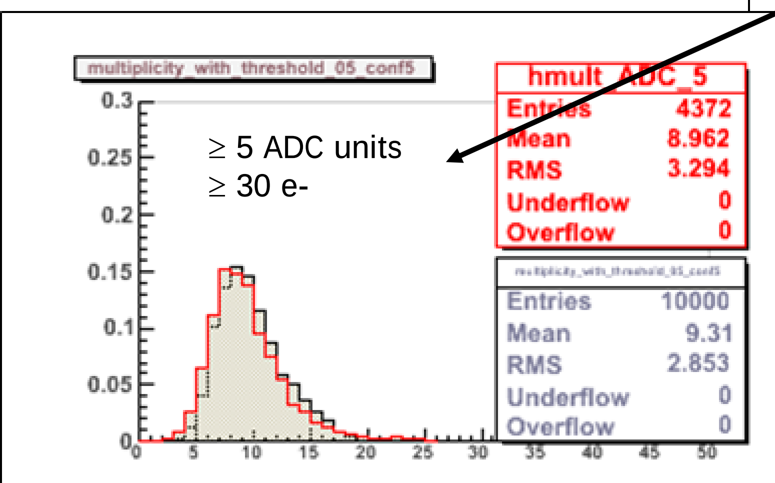
Are results close to real data ?

DIGMAPS: Some preliminary results (20 um pitch)

- Nothing optimized !
  - DIGMAPS model
  - DATA
- Mulitiplicity distribution
  - Number of pixels in cluster
  - For different ADC cuts

1 ADC unit ~ 5.9 e-
(Noise = 9.2 e-)

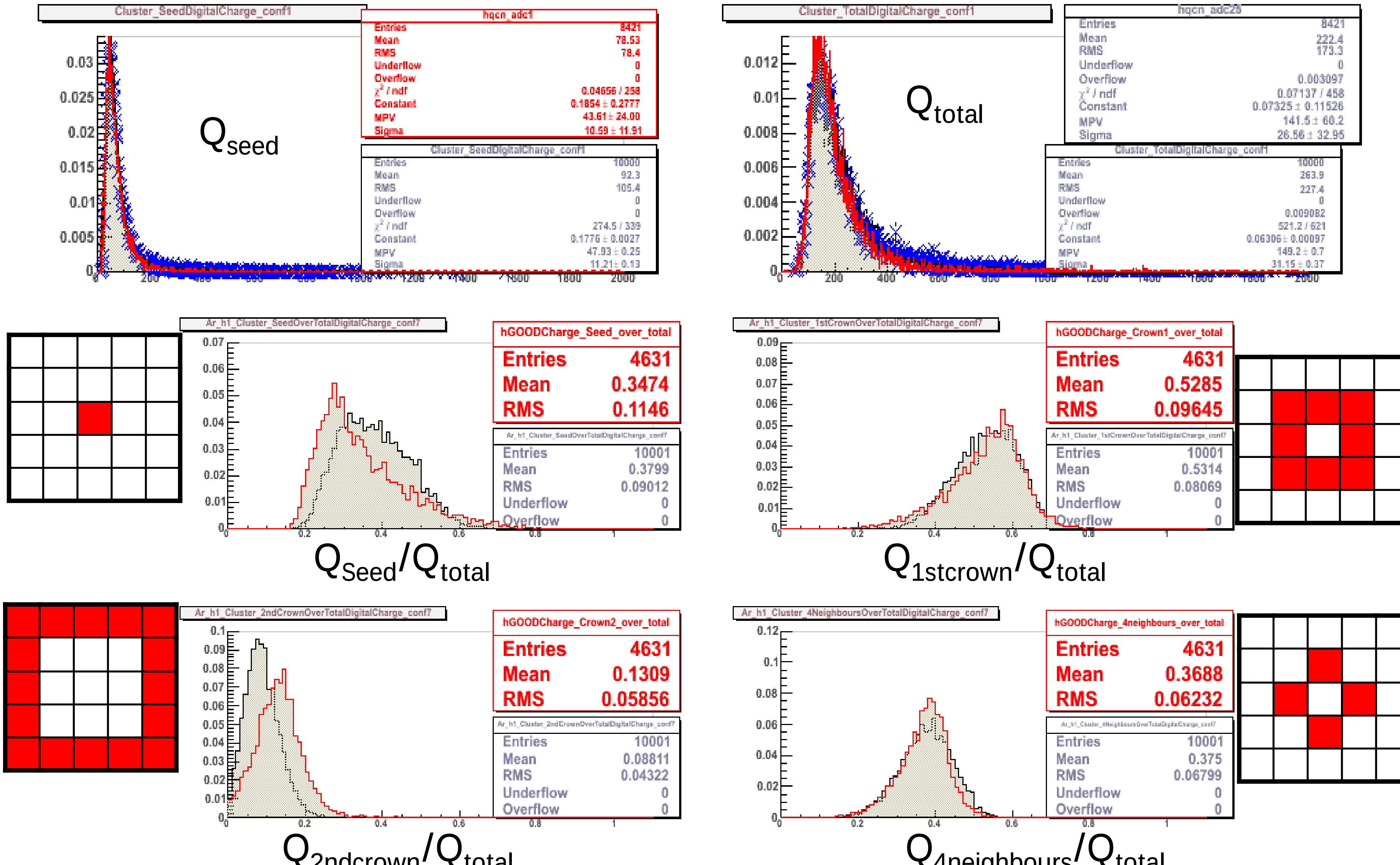




DIGMAPS model

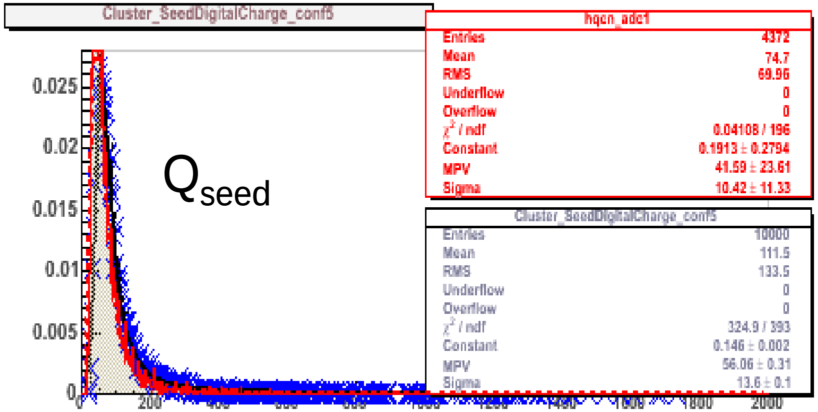
DATA

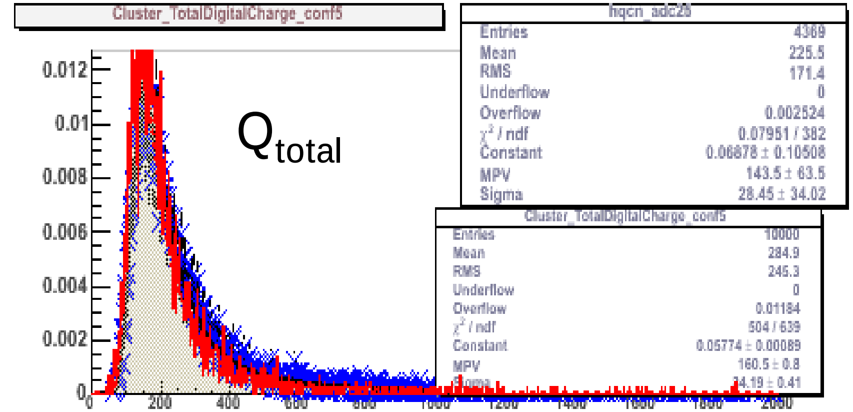
M18 (10μm pitch)

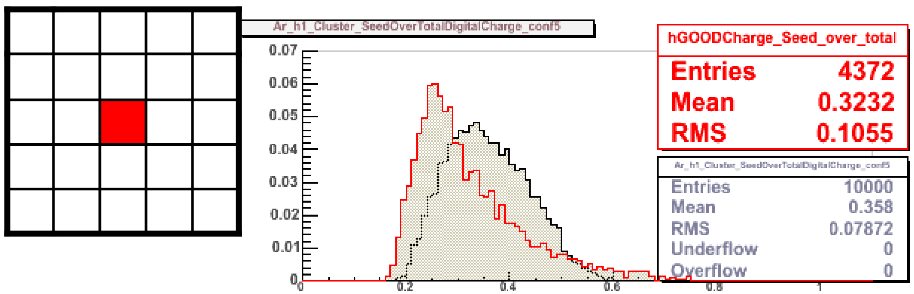


DIGMAPS model
DATA

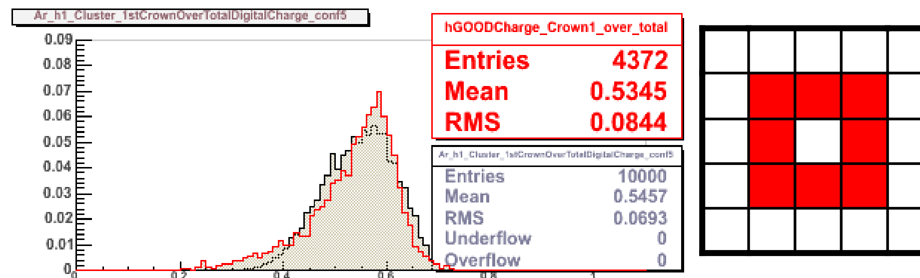
M9 (20μm pitch)



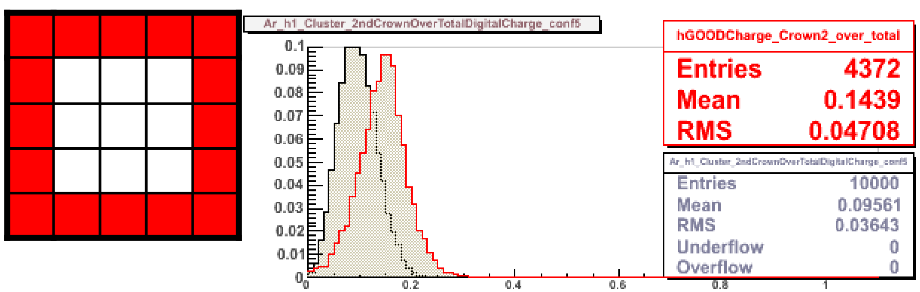


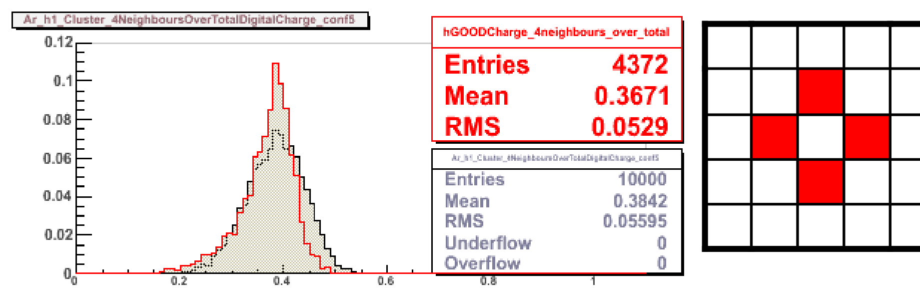


Q_{Seed}/Q_{total}



$Q_{1stcrown}/Q_{total}$





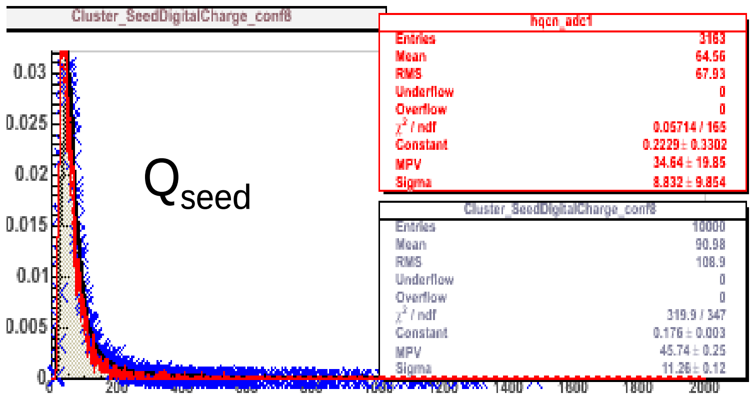
$Q_{2ndcrown}/Q_{total}$

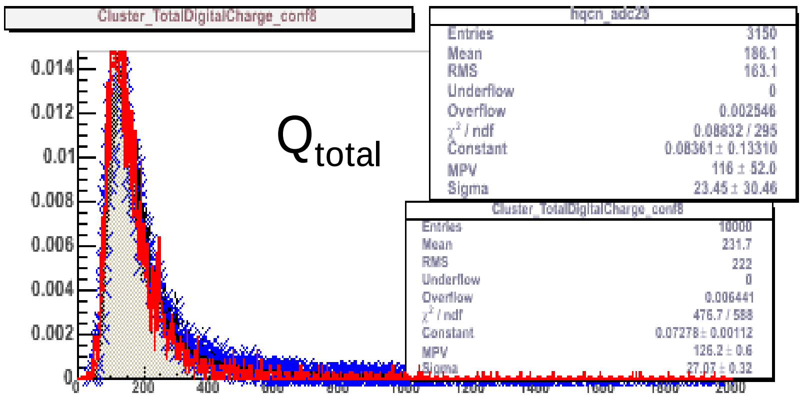
$Q_{4neighbours}/Q_{total}$

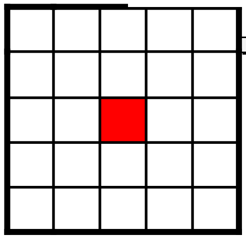
DIGMAPS model

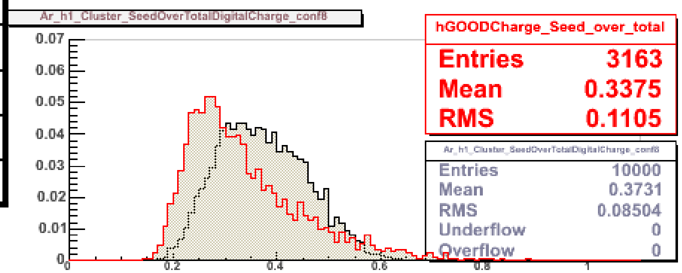
DATA

M9 (30μm pitch)

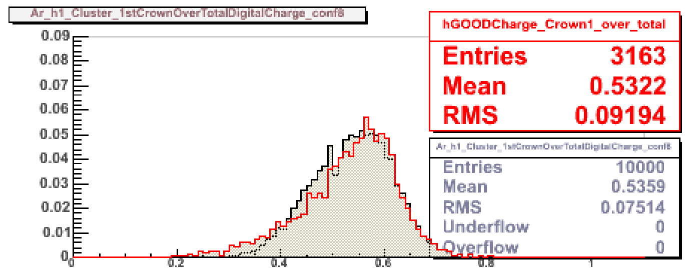


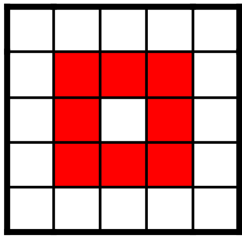




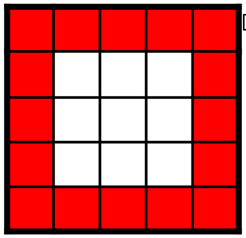


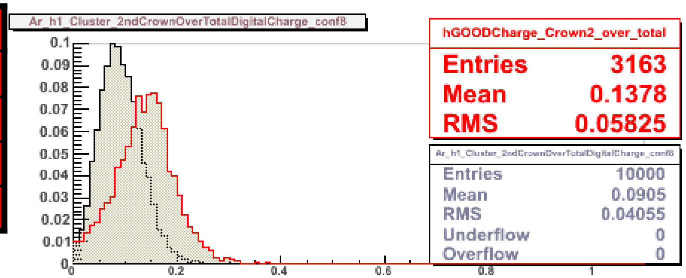
Q_{Seed}/Q_{total}

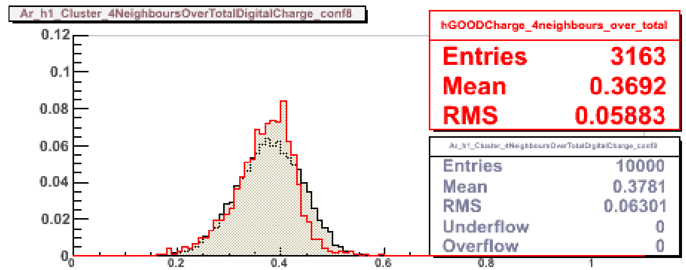


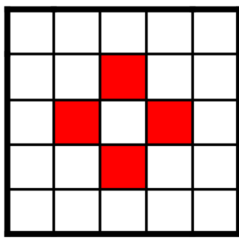


$Q_{1stcrown}/Q_{total}$







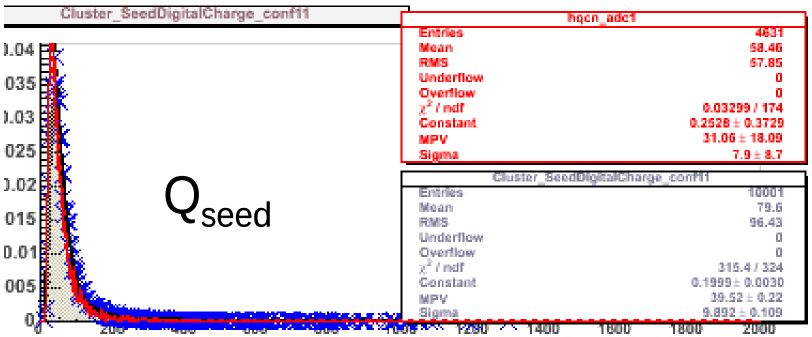


$Q_{2ndcrown}/Q_{total}$ $Q_{4neighbours}/Q_{total}$

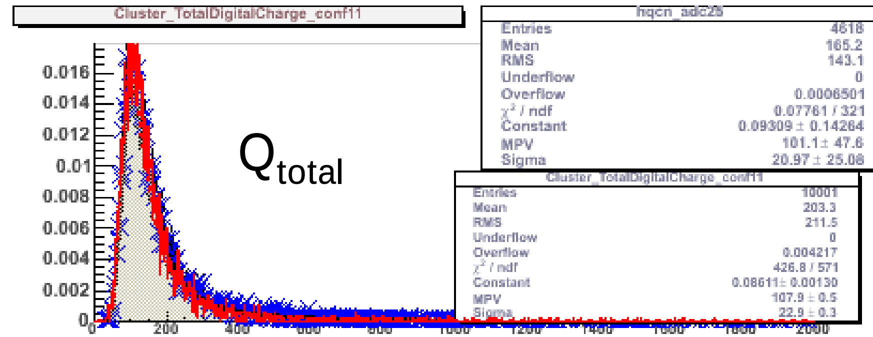
DIGMAPS model

DATA

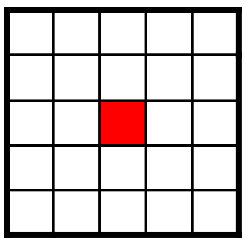
M9 (40μm pitch)

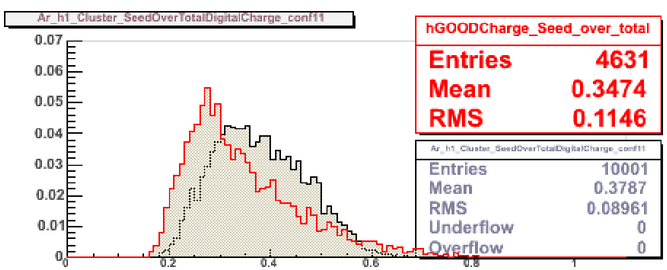


Q_{seed}

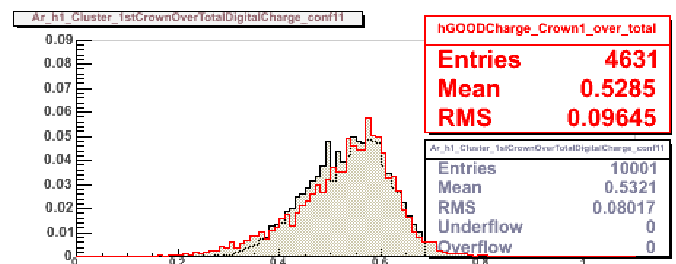


Q_{total}

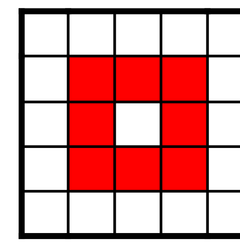


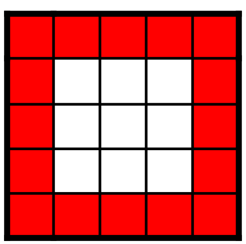


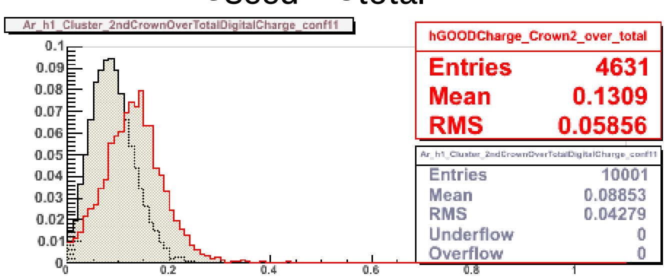
Q_{Seed}/Q_{total}

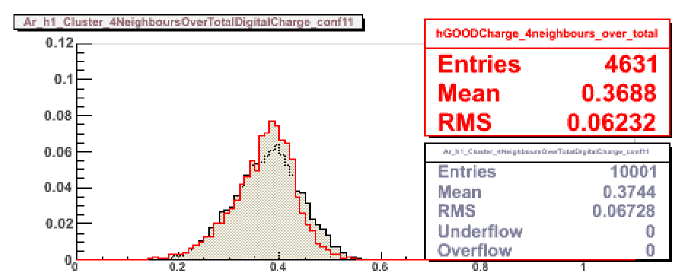


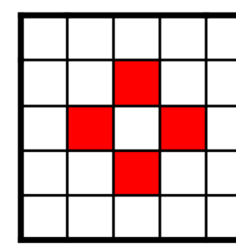
$Q_{1stcrown}/Q_{total}$









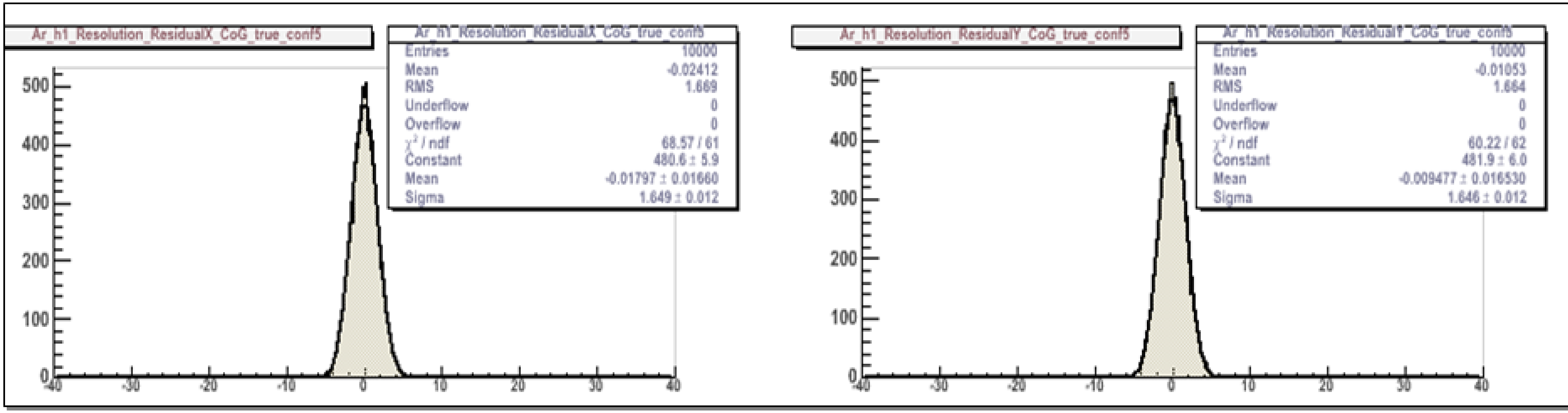


$Q_{2ndcrown}/Q_{total}$

$Q_{4neighbours}/Q_{total}$

Resolution (μm)

- E.g. M9, 20 um pitch



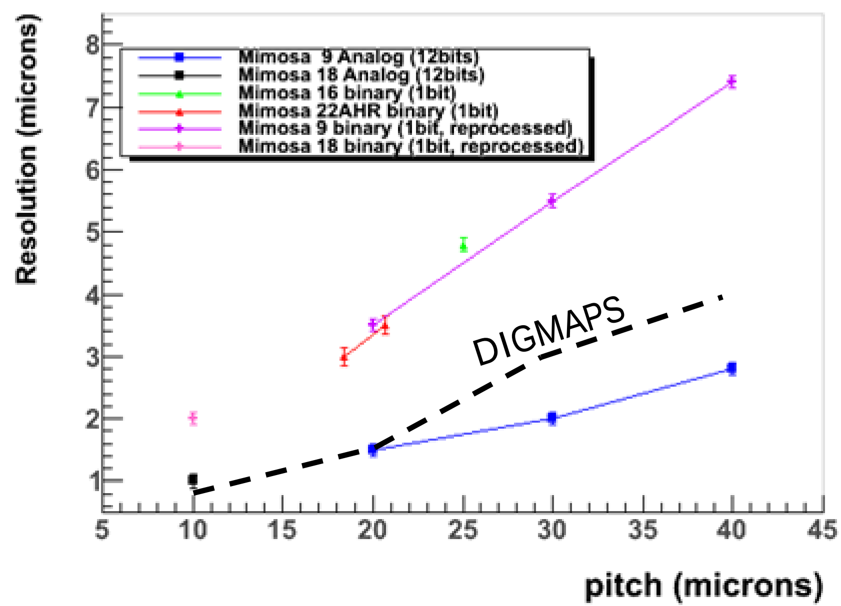
DIGMAPS model

$\sigma_{(CenterofGravity)} \sim 1.7\ \mu m$

DATA

$\sigma_{(CenterofGravity)} \sim 1.8\ \mu m$

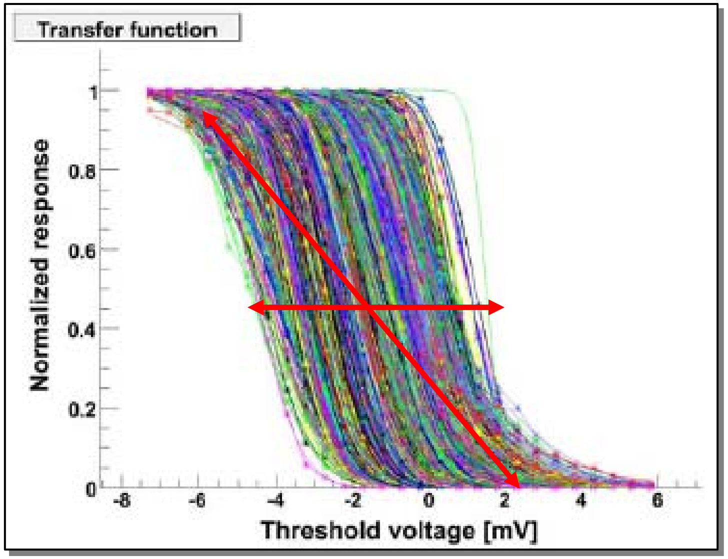
Not so good agreement for larger pitch...



Step 4/5 (ADC and cluster algorithms)

- Under development
  - Only perfect clustering at the moment
  - Only perfect ADC/discri.
    - ➢ Realistic Noise treatment to be added

      FPN + Temporal Noise
    - ➢ Zero suppression to be added



FPN / Temporal Noise

Performances: summary

- Fit / model not optimized
  - Address more carefully the weight of 2nd crown pixels
    - ➢ small number of entries ⇨ uncertainty underestimated
    - ➢ Reduce range of the 2D fit ?
  - Focus should me made on the response of the 8 neighbouring pixels
    - ➢ Determines multiplicity (particularly for digitized chips)
    - ➢ Determines resolution
    - ➢ Determines hit separation performances
  - Global response is already encouraging
    - ➢ Limited number of parameters (Noise, epitaxial layer + 2D double gaussian)
    - ➢ Multiplicity can be reproduced
    - ➢ Still many optimization to be done
  - Model could be simplified
    - ➢ each Q_i of a given segment has to be randomly adressed to one pixel
    - ➢ Option: suppress random part and charge only with PDF values.

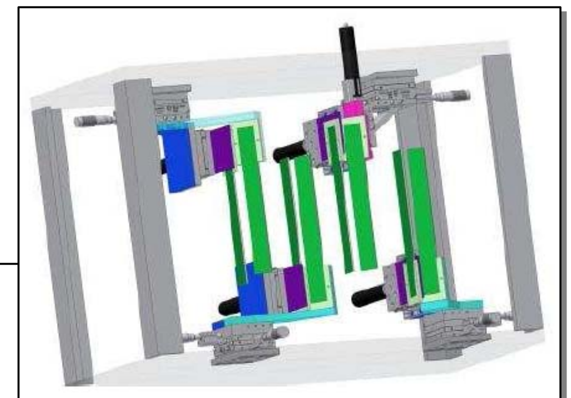
DIGMAPS: summary

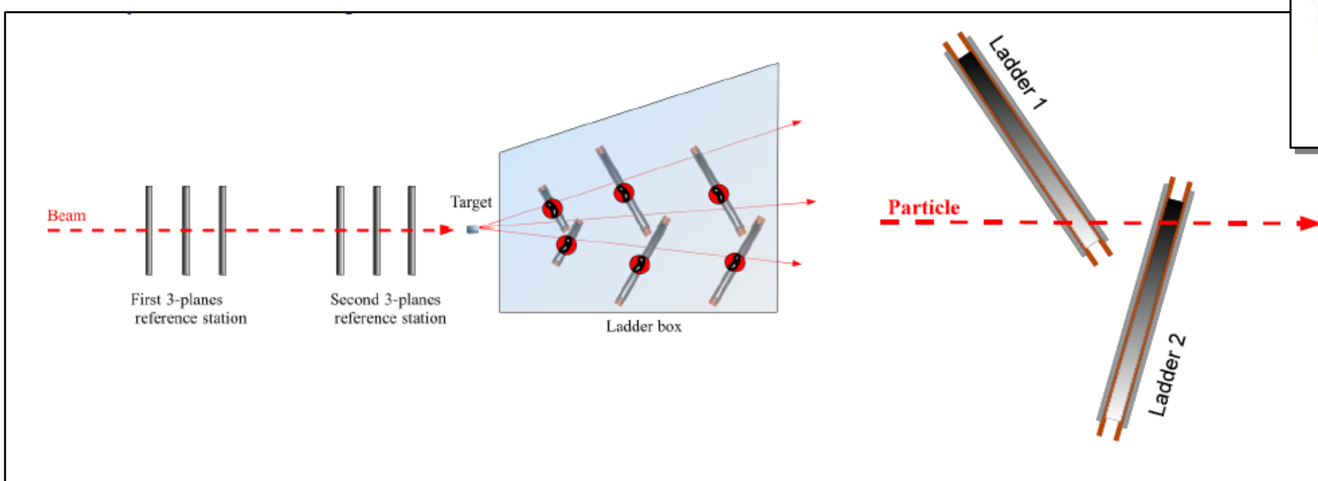
- Tool under development !
- DIGMAPS has been designed as a general tool able to help about
  - Design optimization
  - Digitizer tester for simulations
- Possible studies:
  - sensor(s)/models with a digitised output
  - any other charge transport model
    - Optimize parametrized models for fast sim
  - Optimize ADCs
    - N bits, dynamic range, Noise, etc.
  - clustering algorithms
    - chip occupancy
    - Hit separation performances
  - Zero suppression blocks, etc.
  - Elongated pixels
  - Study incident angle effects
  - CPU performances vs models
- Long term
  - Get a full simulation chain from GEANT4 to reco
    - Tracking/vertexing studies
    - Alignment studies (AIDA, ...)
    - Double sided chips studies (mini vectors)

Back up

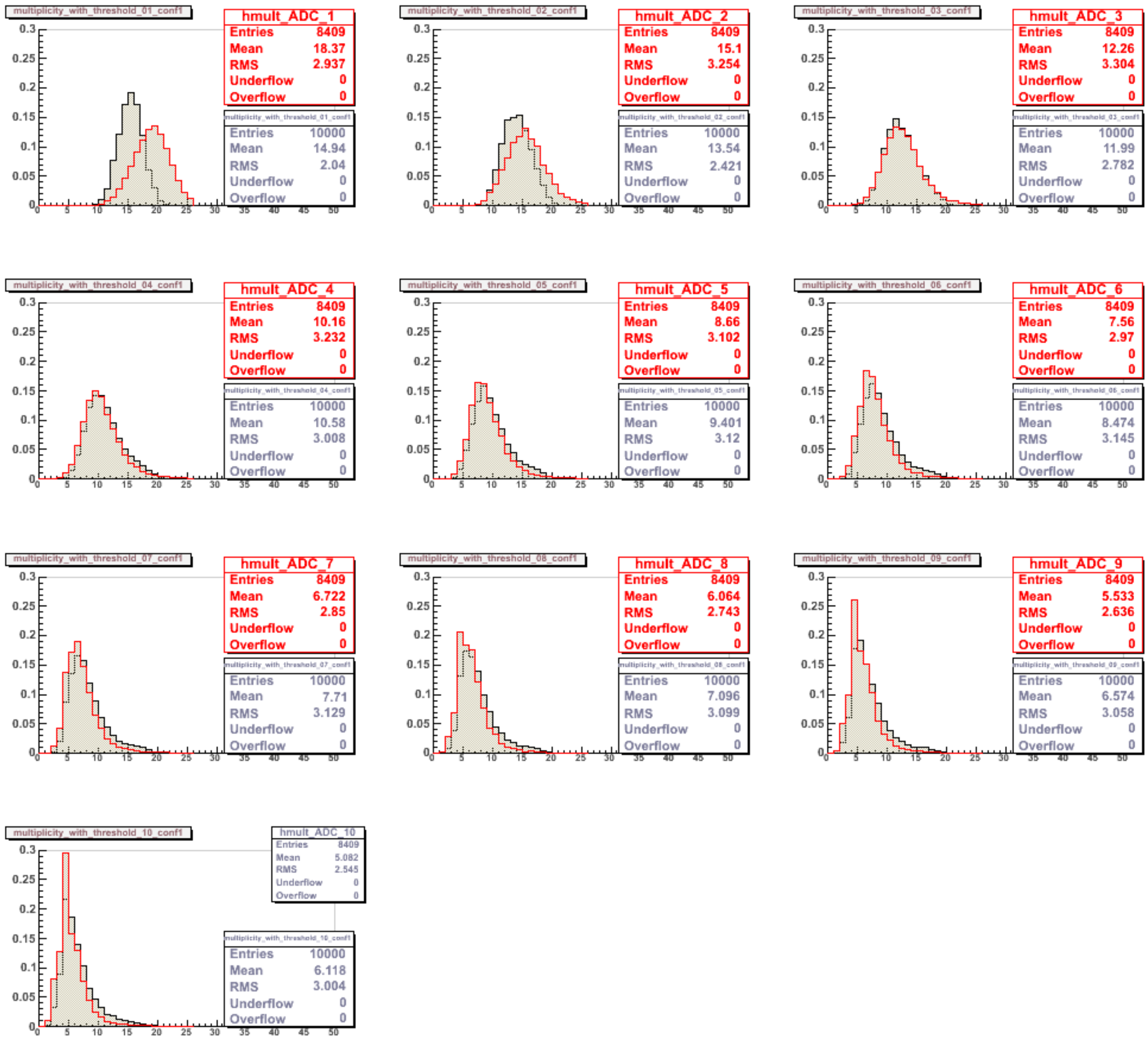
AIDA

- AIDA (EU-FP7 WP9.3) test beam infrastructure (2014)
  - Large area beam tel. (~6x4 cm2)
  - Alignment Investigation Device (AID)
    - ➢ Reproduce a VTX detector sector
    - ➢ Double sided ladders mounted on precise adjustable stages
  - Thermo-mechanical studies



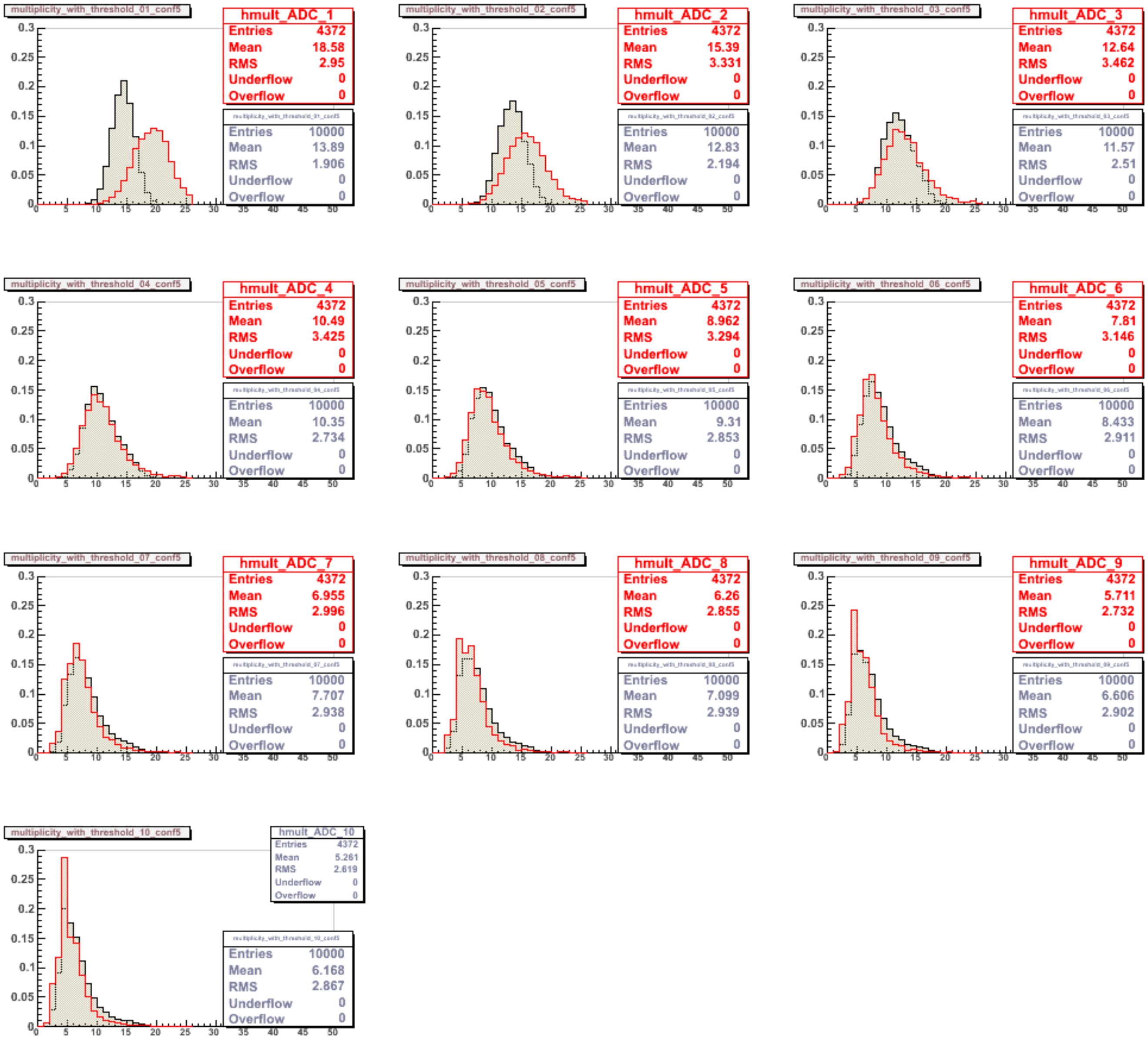


10 um pitch



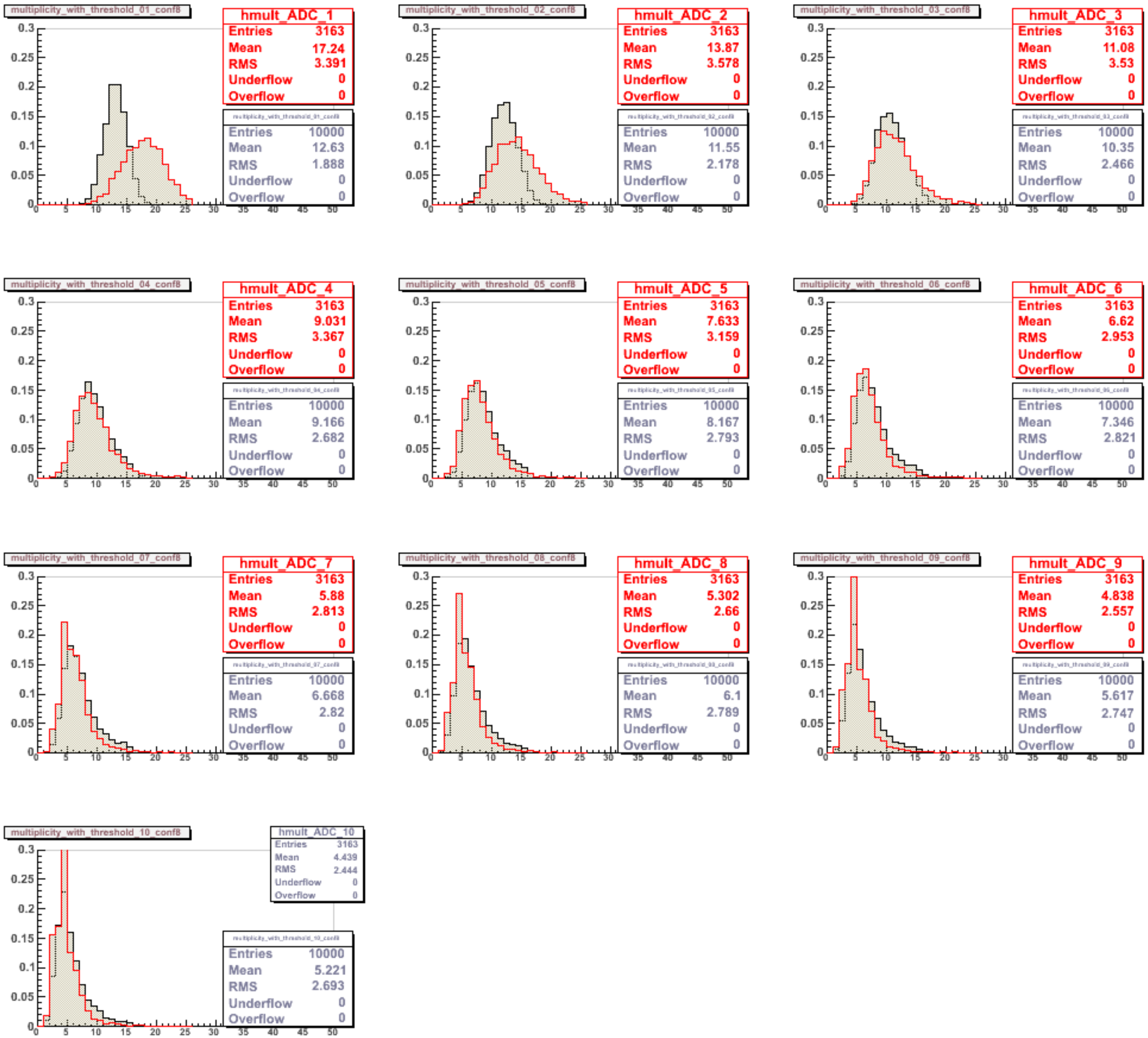
multiplicity_with_threshold_01_conf1
hmult_ADC_1
Entries 8409
Mean 18.37
RMS 2.937
Underflow 0
Overflow 0
multiplicity_with_threshold_01_conf1
Entries 10000
Mean 14.94
RMS 2.04
Underflow 0
Overflow 0
multiplicity_with_threshold_02_conf1
hmult_ADC_2
Entries 8409
Mean 15.1
RMS 3.254
Underflow 0
Overflow 0
multiplicity_with_threshold_02_conf1
Entries 10000
Mean 13.54
RMS 2.421
Underflow 0
Overflow 0
multiplicity_with_threshold_03_conf1
hmult_ADC_3
Entries 8409
Mean 12.26
RMS 3.304
Underflow 0
Overflow 0
multiplicity_with_threshold_03_conf1
Entries 10000
Mean 11.99
RMS 2.782
Underflow 0
Overflow 0
multiplicity_with_threshold_04_conf1
hmult_ADC_4
Entries 8409
Mean 10.16
RMS 3.232
Underflow 0
Overflow 0
multiplicity_with_threshold_04_conf1
Entries 10000
Mean 10.58
RMS 3.008
Underflow 0
Overflow 0
multiplicity_with_threshold_05_conf1
hmult_ADC_5
Entries 8409
Mean 8.66
RMS 3.102
Underflow 0
Overflow 0
multiplicity_with_threshold_05_conf1
Entries 10000
Mean 9.401
RMS 3.12
Underflow 0
Overflow 0
multiplicity_with_threshold_06_conf1
hmult_ADC_6
Entries 8409
Mean 7.56
RMS 2.97
Underflow 0
Overflow 0
multiplicity_with_threshold_06_conf1
Entries 10000
Mean 8.474
RMS 3.145
Underflow 0
Overflow 0
multiplicity_with_threshold_07_conf1
hmult_ADC_7
Entries 8409
Mean 6.722
RMS 2.85
Underflow 0
Overflow 0
multiplicity_with_threshold_07_conf1
Entries 10000
Mean 7.71
RMS 3.129
Underflow 0
Overflow 0
multiplicity_with_threshold_08_conf1
hmult_ADC_8
Entries 8409
Mean 6.064
RMS 2.743
Underflow 0
Overflow 0
multiplicity_with_threshold_08_conf1
Entries 10000
Mean 7.096
RMS 3.099
Underflow 0
Overflow 0
multiplicity_with_threshold_09_conf1
hmult_ADC_9
Entries 8409
Mean 5.533
RMS 2.636
Underflow 0
Overflow 0
multiplicity_with_threshold_09_conf1
Entries 10000
Mean 6.574
RMS 3.058
Underflow 0
Overflow 0
multiplicity_with_threshold_10_conf1
hmult_ADC_10
Entries 8409
Mean 5.082
RMS 2.545
Underflow 0
Overflow 0
multiplicity_with_threshold_10_conf1
Entries 10000
Mean 6.118
RMS 3.004
Underflow 0
Overflow 0

20 um pitch

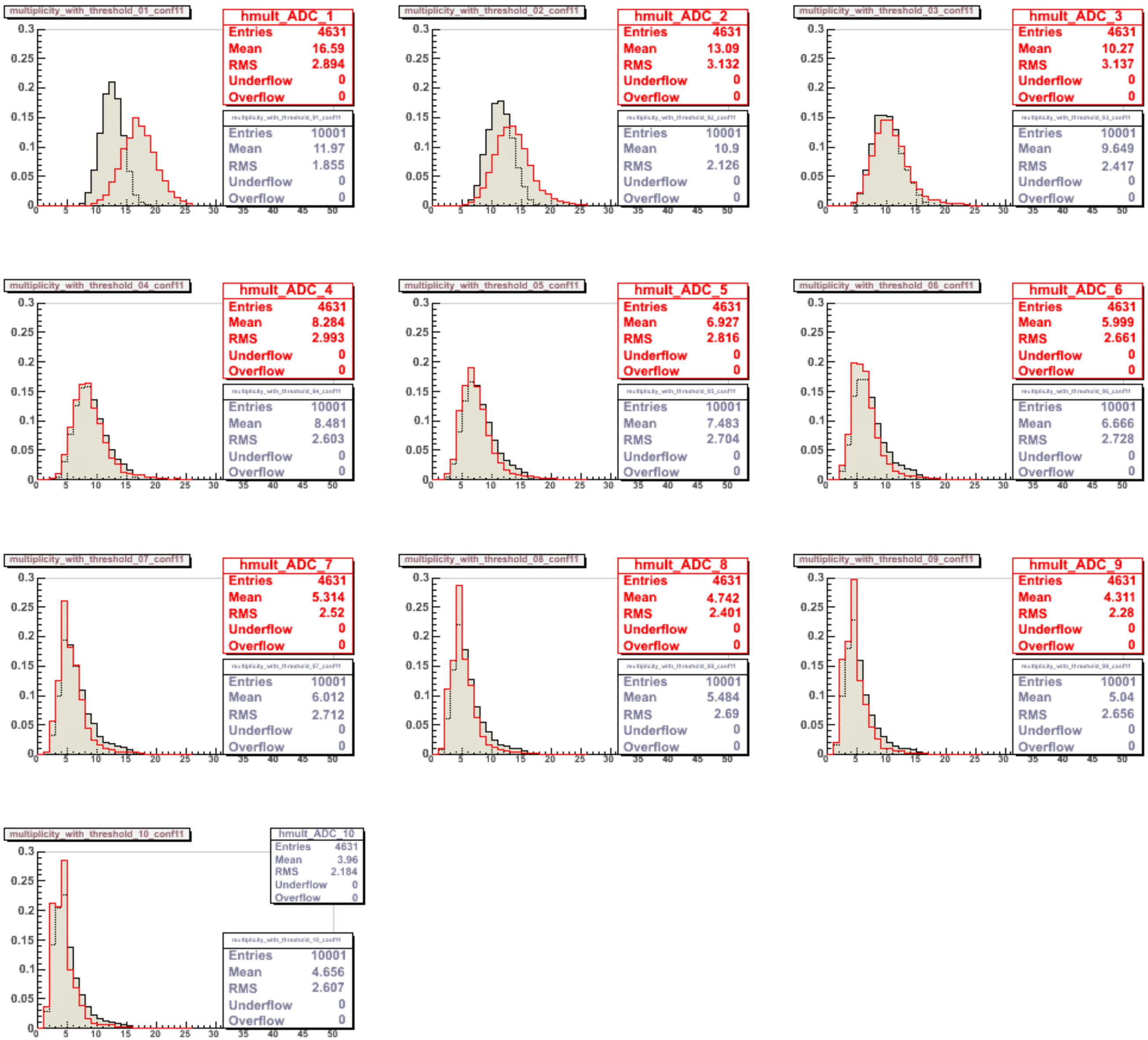


multiplicity_with_threshold_01_conf5
hmult_ADC_1
Entries 4372
Mean 18.58
RMS 2.95
Underflow 0
Overflow 0
Entries 10000
Mean 13.89
RMS 1.906
Underflow 0
Overflow 0
multiplicity_with_threshold_02_conf5
hmult_ADC_2
Entries 4372
Mean 15.39
RMS 3.331
Underflow 0
Overflow 0
Entries 10000
Mean 12.83
RMS 2.194
Underflow 0
Overflow 0
multiplicity_with_threshold_03_conf5
hmult_ADC_3
Entries 4372
Mean 12.64
RMS 3.462
Underflow 0
Overflow 0
Entries 10000
Mean 11.57
RMS 2.51
Underflow 0
Overflow 0
multiplicity_with_threshold_04_conf5
hmult_ADC_4
Entries 4372
Mean 10.49
RMS 3.425
Underflow 0
Overflow 0
Entries 10000
Mean 10.35
RMS 2.734
Underflow 0
Overflow 0
multiplicity_with_threshold_05_conf5
hmult_ADC_5
Entries 4372
Mean 8.962
RMS 3.294
Underflow 0
Overflow 0
Entries 10000
Mean 9.31
RMS 2.853
Underflow 0
Overflow 0
multiplicity_with_threshold_06_conf5
hmult_ADC_6
Entries 4372
Mean 7.81
RMS 3.146
Underflow 0
Overflow 0
Entries 10000
Mean 8.433
RMS 2.911
Underflow 0
Overflow 0
multiplicity_with_threshold_07_conf5
hmult_ADC_7
Entries 4372
Mean 6.955
RMS 2.996
Underflow 0
Overflow 0
Entries 10000
Mean 7.707
RMS 2.938
Underflow 0
Overflow 0
multiplicity_with_threshold_08_conf5
hmult_ADC_8
Entries 4372
Mean 6.26
RMS 2.855
Underflow 0
Overflow 0
Entries 10000
Mean 7.099
RMS 2.939
Underflow 0
Overflow 0
multiplicity_with_threshold_09_conf5
hmult_ADC_9
Entries 4372
Mean 5.711
RMS 2.732
Underflow 0
Overflow 0
Entries 10000
Mean 6.606
RMS 2.902
Underflow 0
Overflow 0
multiplicity_with_threshold_10_conf5
hmult_ADC_10
Entries 4372
Mean 5.261
RMS 2.619
Underflow 0
Overflow 0
Entries 10000
Mean 6.168
RMS 2.867
Underflow 0
Overflow 0

30 um pitch


multiplicity_with_threshold_01_conf8
hmult_ADC_1 Entries 3163 Mean 17.24 RMS 3.391 Underflow 0 Overflow 0
Entries 10000 Mean 12.63 RMS 1.888 Underflow 0 Overflow 0
multiplicity_with_threshold_02_conf8
hmult_ADC_2 Entries 3163 Mean 13.87 RMS 3.578 Underflow 0 Overflow 0
Entries 10000 Mean 11.55 RMS 2.178 Underflow 0 Overflow 0
multiplicity_with_threshold_03_conf8
hmult_ADC_3 Entries 3163 Mean 11.08 RMS 3.53 Underflow 0 Overflow 0
Entries 10000 Mean 10.35 RMS 2.466 Underflow 0 Overflow 0
multiplicity_with_threshold_04_conf8
hmult_ADC_4 Entries 3163 Mean 9.031 RMS 3.367 Underflow 0 Overflow 0
Entries 10000 Mean 9.166 RMS 2.682 Underflow 0 Overflow 0
multiplicity_with_threshold_05_conf8
hmult_ADC_5 Entries 3163 Mean 7.633 RMS 3.159 Underflow 0 Overflow 0
Entries 10000 Mean 8.167 RMS 2.793 Underflow 0 Overflow 0
multiplicity_with_threshold_06_conf8
hmult_ADC_6 Entries 3163 Mean 6.62 RMS 2.953 Underflow 0 Overflow 0
Entries 10000 Mean 7.346 RMS 2.821 Underflow 0 Overflow 0
multiplicity_with_threshold_07_conf8
hmult_ADC_7 Entries 3163 Mean 5.88 RMS 2.813 Underflow 0 Overflow 0
Entries 10000 Mean 6.668 RMS 2.82 Underflow 0 Overflow 0
multiplicity_with_threshold_08_conf8
hmult_ADC_8 Entries 3163 Mean 5.302 RMS 2.66 Underflow 0 Overflow 0
Entries 10000 Mean 6.1 RMS 2.789 Underflow 0 Overflow 0
multiplicity_with_threshold_09_conf8
hmult_ADC_9 Entries 3163 Mean 4.838 RMS 2.557 Underflow 0 Overflow 0
Entries 10000 Mean 5.617 RMS 2.747 Underflow 0 Overflow 0
multiplicity_with_threshold_10_conf8
hmult_ADC_10 Entries 3163 Mean 4.439 RMS 2.444 Underflow 0 Overflow 0
Entries 10000 Mean 5.221 RMS 2.693 Underflow 0 Overflow 0

40 um pitch



hmult_ADC_1
Entries 4631
Mean 16.59
RMS 2.894
Underflow 0
Overflow 0
Entries 10001
Mean 11.97
RMS 1.855
Underflow 0
Overflow 0
hmult_ADC_2
Entries 4631
Mean 13.09
RMS 3.132
Underflow 0
Overflow 0
Entries 10001
Mean 10.9
RMS 2.126
Underflow 0
Overflow 0
hmult_ADC_3
Entries 4631
Mean 10.27
RMS 3.137
Underflow 0
Overflow 0
Entries 10001
Mean 9.649
RMS 2.417
Underflow 0
Overflow 0
hmult_ADC_4
Entries 4631
Mean 8.284
RMS 2.993
Underflow 0
Overflow 0
Entries 10001
Mean 8.481
RMS 2.603
Underflow 0
Overflow 0
hmult_ADC_5
Entries 4631
Mean 6.927
RMS 2.816
Underflow 0
Overflow 0
Entries 10001
Mean 7.483
RMS 2.704
Underflow 0
Overflow 0
hmult_ADC_6
Entries 4631
Mean 5.999
RMS 2.661
Underflow 0
Overflow 0
Entries 10001
Mean 6.666
RMS 2.728
Underflow 0
Overflow 0
hmult_ADC_7
Entries 4631
Mean 5.314
RMS 2.52
Underflow 0
Overflow 0
Entries 10001
Mean 6.012
RMS 2.712
Underflow 0
Overflow 0
hmult_ADC_8
Entries 4631
Mean 4.742
RMS 2.401
Underflow 0
Overflow 0
Entries 10001
Mean 5.484
RMS 2.69
Underflow 0
Overflow 0
hmult_ADC_9
Entries 4631
Mean 4.311
RMS 2.28
Underflow 0
Overflow 0
Entries 10001
Mean 5.04
RMS 2.656
Underflow 0
Overflow 0
hmult_ADC_10
Entries 4631
Mean 3.96
RMS 2.184
Underflow 0
Overflow 0
Entries 10001
Mean 4.656
RMS 2.607
Underflow 0
Overflow 0